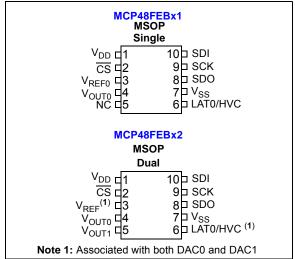


# 8-/10-/12-Bit Single/Dual Voltage Output Nonvolatile Digital-to-Analog Converters with SPI Interface

#### **Features**

- · Operating Voltage Range:
  - 2.7V to 5.5V full specifications
  - 1.8V to 2.7V reduced device specifications
- · Output Voltage Resolutions:
  - 8-bit: MCP48FEB0X (256 Steps)
  - 10-bit: MCP48FEB1X (1024 Steps)
  - 12-bit: MCP48FEB2X (4096 Steps)
- · Rail-to-Rail Output
- Fast Settling Time of 7.8 µs (typical)
- · DAC Voltage Reference Source Options:
  - Device V<sub>DD</sub>
  - External V<sub>REF</sub> pin (buffered or unbuffered)
  - Internal Band Gap (1.22V typical)
- · Output Gain Options:
  - Unity (1x)
  - 2x
- Nonvolatile Memory (EEPROM):
  - User-programmed Power-on Reset (POR)/Brown-out Reset (BOR) output setting, recall and device configuration bits
  - Auto Recall of Saved DAC register setting
  - Auto Recall of Saved Device Configuration (Voltage Reference, Gain, Power-Down)
- · Power-on/Brown-out Reset Protection
- · Power-Down Modes:
  - Disconnects output buffer (High Impedance)
  - Selection of  $V_{OUT}$  pull-down resistors (100 k $\Omega$  or 1 k $\Omega$ )
- · Low Power Consumption:
  - Normal operation: <180 μA (Single), 380 μA (Dual)
  - Power-down operation: 650 nA typical
  - EEPROM write cycle (1.9 mA maximum)
- · SPI Interface:
  - Supports '00' and '11' modes
  - Up to 20 MHz writes and 10 MHz reads
  - Input buffers support interfacing to low-voltage digital devices
- Package Types: 10-lead MSOP
- Extended Temperature Range: -40°C to +125°C

#### **Package Types**



#### **General Description**

The MCP48FEBXX are Single- and Dual-channel 8-bit, 10-bit, and 12-bit buffered voltage output Digital-to-Analog Converters (DAC) with nonvolatile memory and an SPI serial interface.

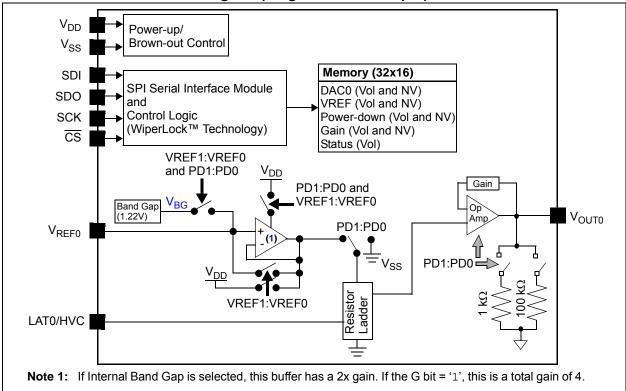
The  $V_{REF}$  pin, the device  $V_{DD}$  or the internal band gap voltage can be selected as the DAC's reference voltage. When  $V_{DD}$  is selected,  $V_{DD}$  is connected internally to the DAC reference circuit. When the  $V_{REF}$  pin is used, the user can select the output buffer's gain to be 1 or 2. When the gain is 2, the  $V_{REF}$  pin voltage should be limited to a maximum of  $V_{DD}/2$ .

These devices have an SPI-compatible serial interface. Write commands are supported up to 20 MHz while read commands are supported up to 10 MHz.

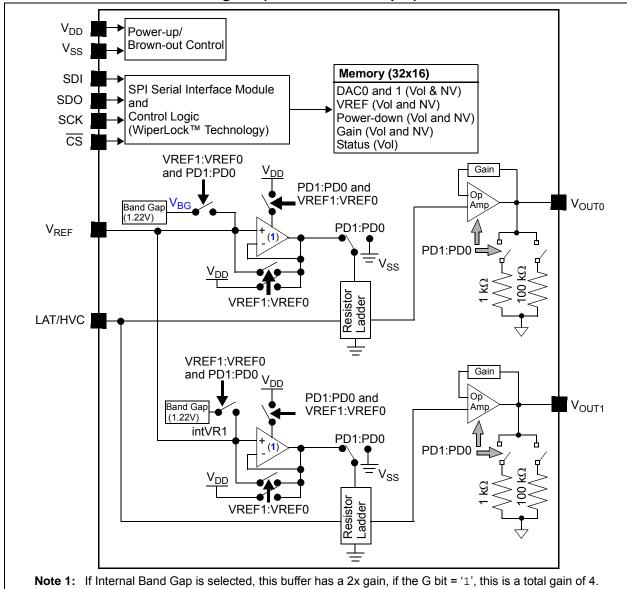
#### **Applications**

- · Set Point or Offset Trimming
- Sensor Calibration
- · Low-Power Portable Instrumentation
- · PC Peripherals
- · Data Acquisition Systems
- · Motor Control

#### MCP48FEBX1 Device Block Diagram (Single-Channel Output)



#### MCP48FEBX2 Device Block Diagram (Dual-Channel Output)



#### **Device Features**

Device	# of Channels	Resolution (bits)	Control Interface	DAC Output POR/BOR Setting <sup>(1)</sup>	# of VREF Inputs	Internal band gap ?	# of LAT Inputs	Memory	Specified Operating Range (V <sub>DD</sub> ) <sup>(2)</sup>
MCP48FEB01	1	8	SPI	7Fh	1	Yes	1	EEPROM	1.8V to 5.5V
MCP48FEB11	1	10	SPI	1FFh	1	Yes	1	EEPROM	1.8V to 5.5V
MCP48FEB21	1	12	SPI	7FFh	1	Yes	1	EEPROM	1.8V to 5.5V
MCP48FEB02	2	8	SPI	7Fh	1	Yes	1	EEPROM	1.8V to 5.5V
MCP48FEB12	2	10	SPI	1FFh	1	Yes	1	EEPROM	1.8V to 5.5V
MCP48FEB22	2	12	SPI	7FFh	1	Yes	1	EEPROM	1.8V to 5.5V
MCP47FVB01	1	8	I <sup>2</sup> C™	7Fh	1	Yes	1	RAM	1.8V to 5.5V
MCP47FVB11	1	10	I <sup>2</sup> C	1FFh	1	Yes	1	RAM	1.8V to 5.5V
MCP47FVB21	1	12	I <sup>2</sup> C	7FFh	1	Yes	1	RAM	1.8V to 5.5V
MCP47FVB02	2	8	I <sup>2</sup> C	7Fh	1	Yes	1	RAM	1.8V to 5.5V
MCP47FVB12	2	10	I <sup>2</sup> C	1FFh	1	Yes	1	RAM	1.8V to 5.5V
MCP47FVB22	2	12	I <sup>2</sup> C	7FFh	1	Yes	1	RAM	1.8V to 5.5V
MCP47FEB01	1	8	I <sup>2</sup> C	7Fh	1	Yes	1	EEPROM	1.8V to 5.5V
MCP47FEB11	1	10	I <sup>2</sup> C	1FFh	1	Yes	1	EEPROM	1.8V to 5.5V
MCP47FEB21	1	12	I <sup>2</sup> C	7FFh	1	Yes	1	EEPROM	1.8V to 5.5V
MCP47FEB02	2	8	I <sup>2</sup> C	7Fh	1	Yes	1	EEPROM	1.8V to 5.5V
MCP47FEB12	2	10	I <sup>2</sup> C	1FFh	1	Yes	1	EEPROM	1.8V to 5.5V
MCP47FEB22	2	12	I <sup>2</sup> C	7FFh	1	Yes	1	EEPROM	1.8V to 5.5V

Note 1: Factory Default value. The DAC output POR/BOR value can be modified via the nonvolatile DAC output register(s) (available only on nonvolatile devices (MCP4XFEBXX)).

<sup>2:</sup> Analog output performance specified from 2.7V to 5.5V.

#### 1.0 ELECTRICAL CHARACTERISTICS

### Absolute Maximum Ratings (†)

Voltage on $V_{DD}$ with respect to $V_{SS}$	-0.6V to +6.5V	
Voltage on all pins with respect to V	'ss ·····	-0.6V to V <sub>DD</sub> +0.3V
Input clamp current, $I_{IK}$ ( $V_I < 0, V_I >$	$V_{DD}$ , $V_{I} > V_{PP}$ on HV pins) .	±20 mA
Output clamp current, $I_{OK}$ ( $V_O < 0$ c	or V <sub>O</sub> > V <sub>DD</sub> )	±20 mA
Maximum current out of $V_{SS}$ pin		50 mA
Maximum current into V <sub>DD</sub> pin		50 mA 100 mA
Maximum current sourced by the V	<sub>OUT</sub> pin	20 mA
Maximum current sunk by the $V_{\text{OUT}}$	- pin	20 mA
Maximum current sunk by the V <sub>REF</sub>	pin	125 μA
Maximum input current source/sunk	by SDI, SCK, and $\overline{\text{CS}}$ pins	2 mA
Maximum output current sunk by Si	DO Output pin	25 mA
Total power dissipation (1)		400 mW
Package power dissipation (T <sub>A</sub> = +5 MSOP-10	50°C, T <sub>J</sub> = +150°C)	490 mW
		≥ ±4 kV (HBM) ≥ ±400V (MM)
		≥±1.5 kV (CDM)
Latch-Up (per JEDEC JESD78A) @	) +125°C	±100 mA
Storage temperature	65°C to +150°C	
Ambient temperature with power ap	55°C to +125°C	
Soldering temperature of leads (10	+300°C	
Maximum Junction Temperature (T	+150°C	

**† Notice:** Stresses above those listed under "Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Note 1: Power dissipation is calculated as follows:

 $P_{DIS} = V_{DD} x \{I_{DD} - \sum I_{OH}\} + \sum \{(V_{DD} - V_{OH}) x I_{OH}\} + \sum (V_{OL} x I_{OL})$ 

### **DC CHARACTERISTICS**

DC Characteristics	Standard Operating Conditions (unless otherwise specified): Operating Temperature: -40°C $\leq$ T <sub>A</sub> $\leq$ +125°C (Extended) Unless otherwise noted, all parameters apply across these specified operating ranges: V <sub>DD</sub> = +2.7V to 5.5V, V <sub>REF</sub> = +2.048V to V <sub>DD</sub> , V <sub>SS</sub> = 0V Gx = '0', R <sub>L</sub> = 5 k\Omega from V <sub>OUT</sub> to V <sub>SS</sub> , C <sub>L</sub> = 100 pF Typical specifications represent values for V <sub>DD</sub> = 5.5V, T <sub>A</sub> = +25°C.										
Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions					
Supply Voltage	$V_{DD}$	2.7	_	5.5	V						
		1.8	_	2.7	V	DAC operation (reduced analog specifications) and Serial Interface					
V <sub>DD</sub> Voltage (rising) to ensure device Power-on Reset	V <sub>POR/BOR</sub>	_	_	1.7	V	RAM retention voltage (V <sub>RAM</sub> ) < V <sub>POR</sub> V <sub>DD</sub> voltages greater than V <sub>POR/BOR</sub> limit Ensure that device is out of reset.					
V <sub>DD</sub> Rise Rate to ensure Power-on Reset	$V_{\mathrm{DDRR}}$		(Note	3)	V/ms						
High-Voltage Commands Voltage Range (HVC pin)	V <sub>HV</sub>	V <sub>SS</sub>	_	12.5	V	The HVC pin will be at one of three input levels (V <sub>IL</sub> , V <sub>IH</sub> or V <sub>IHH</sub> ) <sup>(1)</sup>					
High-Voltage Input Entry Voltage	V <sub>IHHEN</sub>	9.0	_	_	V	Threshold for Entry into WiperLock Technology					
High-Voltage Input Exit Voltage	V <sub>IHHEX</sub>	_	_	V <sub>DD</sub> + 0.8V	V	(Note 2)					
Power-on Reset to Out- put-Driven Delay	T <sub>PORD</sub>	_	25	50	μs	$V_{DD}$ rising, $V_{DD} > V_{POR}$					

Note 1 This parameter is ensured by design.

Note 2 This parameter is ensured by characterization.

Note 3 POR/BOR voltage trip point is not slope dependent. Hysteresis implemented with time delay.

	DC Characteris	etics	Standard Operating Conditions (unless otherwise specified): Operating Temperature: $-40^{\circ}\text{C} \le T_{A} \le +125^{\circ}\text{C}$ (Extended) Unless otherwise noted, all parameters apply across these specified operating ranges: $V_{DD} = +2.7 \text{V}$ to 5.5V, $V_{REF} = +2.048 \text{V}$ to $V_{DD}$ , $V_{SS} = 0 \text{V}$ Gx = '0', $V_{CD} = 100 \text{ N}$ from $V_{CD} = 100 \text{ N}$ Typical specifications represent values for $V_{DD} = 100 \text{ N}$ from $V_{CD} = 100 \text{ N}$ Typical specifications represent values for $V_{DD} = 100 \text{ N}$ from $V_{CD} = 100  $									
	Parameters	Sym.	Min.	Тур.	Max.	Units			Conditions			
	Supply Current	I <sub>DD</sub>	_	_	320	μΑ	Single	1MHz <sup>(2)</sup>				
1.7 mA 20MHz Vout is unloaded, V <sub>DD</sub> = 5 volatile DAC Register = 00 v			_	_	910	μA		10MHz (2)	(Not High-Voltage Command)			
			_	_	1.7	mA		20MHz				
—         1.85         mA         20MHz           —         250         μA         Single         1MHz (²)         Serial Interface Active (Not High-Voltage Command VRB:VRxA = '10' (⁴)         VXRB:VRxA = '10' (⁴)         VXRB:VRxA = '10' (⁴)         VOUT is unloaded.         VoIt is DAC Register = 0.00         VRXB:VRxA = '00'         ScK = SDI = VSS         VoUT is unloaded.         VoIt is unloaded.			_	_	510	μΑ	Dual	1MHz <sup>(2)</sup>	Volatile DAC Register = 000h			
250 μA Single 1MHz (2) 10MHz (2) 10MHz (2) 20MHz (			_	_	1.1	mA		10MHz (2)	]			
— — 840			_	_	1.85	mA	1	20MHz				
— — 1.65			_	_	250	μΑ	Single	1MHz <sup>(2)</sup>	Serial Interface Active			
—   1.65 mA   20MHz (²)   V <sub>QUT</sub> is unloaded.   V <sub>REF</sub> = V <sub>DD</sub> = 5.5V   Volatile DAC Register = 0.0   V <sub>REF</sub> = V <sub>DD</sub> = 5.5V   Volatile DAC Register = 0.0   V <sub>REF</sub> = V <sub>DD</sub> = 5.5V   Volatile DAC Register = 0.0   V <sub>REF</sub> = V <sub>DD</sub> = 5.5V   Volatile DAC Register = 0.0   V <sub>REF</sub> = V <sub>DD</sub> = 5.5V   Volatile DAC Register = 0.0   V <sub>REF</sub> = V <sub>DD</sub>   V <sub>REF</sub> = V <sub>DD</sub> = 5.5V   V <sub>REF</sub> = V <sub>DD</sub>   V <sub>REF</sub>   V <sub>DD</sub> = 5.5V   V <sub>REF</sub>   V <sub>DD</sub>   V <sub>REF</sub>   V <sub>DD</sub>   V <sub>REF</sub>   V <sub>DD</sub> = 5.5V   V <sub>REF</sub>   V <sub>DD</sub>   V <sub>REF</sub>   V <sub>DD</sub> = 5.5V   V <sub>DE</sub>   V <sub>DD</sub> = 5.5V   V <sub>DD</sub> = 5.5V   V <sub>DD</sub>   V <sub>DD</sub> = 5.5V   V <sub>DD</sub> = 5.5V   V <sub>DD</sub> = 5.5V   V <sub>DD</sub>   V <sub>DD</sub>   V <sub>DD</sub>   V <sub>DD</sub> = 5.5V   V <sub>DD</sub>   V <sub>DD</sub>   V <sub>DD</sub>   V <sub>DD</sub>   V <sub>DD</sub>   V <sub>DD</sub>			_	_	840	μΑ		10MHz (2)	(Not High-Voltage Command)			
380 μA Dual 1MHz (²) VREF = VDD = 5.5V Volatile DAC Register = 0.0			_	_	1.65	mA	1	20MHz <sup>(2)</sup>				
—   970			_	_	380	μΑ	Dual	1MHz <sup>(2)</sup>				
			_	_	970	μΑ		10MHz (2)	Volatile DAC Register = 000h			
380 μA Dual (Not High-Voltage Command) VRxB:VRxA = '00' SCK = SDI = V <sub>SS</sub> V <sub>OUT</sub> is unloaded. Volatile DAC Register = 000th Script Interface Inactive (2) (Not High-Voltage Command) VRxB:VRxA = '11', V <sub>REF</sub> = V <sub>DD</sub> SCK = SDI = V <sub>SS</sub> V <sub>OUT</sub> is unloaded. Volatile DAC Register = 000th SCK = SDI = V <sub>SS</sub> V <sub>OUT</sub> is unloaded. Volatile DAC Register = 000th V <sub>REF</sub> = V <sub>DD</sub> = 5.5V (After write, Serial Interface is Inactive.) Write all 0's to non-volatile DAC 0 (address 10th V <sub>OUT</sub> pins are unloaded.  - 145 180 μA Single HVC = 12.5V (High-Voltage Command Serial Interface Inactive V <sub>REF</sub> = V <sub>DD</sub> = 5.5V, LAT/HVC = V <sub>IHH</sub> DAC registers = 000th V <sub>OUT</sub> pins are unloaded.			_	_	1.75	mA		20MHz (2)				
VRxB:VRxA = '00'   SCK = SDI = V <sub>SS</sub>   V <sub>OUT</sub> is unloaded. Volatile DAC Register = 000h			_		180	μA	Single					
- 380 μA Dual (Not High-Voltage Command) VRxB:VRxA = '11', V <sub>REF</sub> = V <sub>DD</sub> SCK = SDI = V <sub>SS</sub> V <sub>OUT</sub> is unloaded. Volatile DAC Register = 000h  - 1.9 mA EE Write Current V <sub>REF</sub> = V <sub>DD</sub> = 5.5V (After write, Serial Interface is Inactive.) Write all 0's to non-volatile DAC 0 (address 10h V <sub>OUT</sub> pins are unloaded.  - 145 180 μA Single HVC = 12.5V (High-Voltage Command Serial Interface Inactive V <sub>REF</sub> = V <sub>DD</sub> = 5.5V, LAT/HVC = V <sub>IHH</sub> DAC registers = 000h V <sub>OUT</sub> pins are unloaded.			_	_	380	μA	Dual	VRxB:VRx SCK = SD V <sub>OUT</sub> is un	A = '00' I = V <sub>SS</sub> lloaded.			
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			_	_	180	μA	Single	Serial Inter	rface Inactive <sup>(2)</sup>			
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			_	_	380	μА	Dual	VRxB:VRx SCK = SD V <sub>OUT</sub> is un	$A = '11', V_{REF} = V_{DD}$ $I = V_{SS}$ sloaded.			
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			_	_	1.9	mA	V <sub>REF</sub> = (After w Write al	V <sub>DD</sub> = 5.5V vrite, Serial I Il 0's to non-	nterface is Inactive.) volatile DAC 0 (address 10h).			
$V_{REF} = V_{DD} = 5.5V$ , LAT/HVC = $V_{IHH}$ DAC registers = 000h $V_{OUT}$ pins are unloaded.				145	180	μA	Single					
(5)			_	260	400	μA	Dual	V <sub>REF</sub> = V <sub>D</sub> DAC regis	<sub>D</sub> = 5.5V, LAT/HVC = V <sub>IHH</sub> ters = 000h			
Power-Down I <sub>DDP</sub> — 0.65 3.8 μA PDxB:PDxA = '01' (5),	Power-Down	I <sub>DDP</sub>	_	0.65	3.8	μA		PDxA = '01'	(5) <sub>,</sub>			

Note 2 This parameter is ensured by characterization.

Note 4 Supply current is independent of current through the resistor ladder in mode VRxB:VRxA = '10'.

V<sub>OUT</sub> not connected

Note 5 The PDxB:PDxA = '01', '10', and '11' configurations should have the same current.

Note 6 By design, this is the worst-case current mode.

Current

DC Characteristics	Standard Operating Conditions (unless otherwise specified): Operating Temperature: $-40^{\circ}\text{C} \le T_{A} \le +125^{\circ}\text{C}$ (Extended) Unless otherwise noted, all parameters apply across these specified operating ranges: $V_{DD} = +2.7V$ to $5.5V$ , $V_{REF} = +2.048V$ to $V_{DD}$ , $V_{SS} = 0V$ $Gx = '0'$ , $R_{L} = 5$ k $\Omega$ from $V_{OUT}$ to $V_{SS}$ , $C_{L} = 100$ pF Typical specifications represent values for $V_{DD} = 5.5V$ , $T_{A} = +25^{\circ}\text{C}$ .									
Parameters	Sym. Min. Typ. Max. Units Conditions									
Resistor Ladder Resistance	$R_{L}$	100	140	180	kΩ	1.8V ≤ V <sub>REF</sub> ≥	V <sub>DD</sub> ≤ 5.5V : 1.0V <sup>(7)</sup>			
Resolution	N		256		Taps	8-bit	No Missing Codes			
(# of Resistors			1024		Taps	10-bit	No Missing Codes			
and # of Taps) (see B.1 "Resolution")			4096			12-bit	No Missing Codes			
Nominal V <sub>OUT</sub> Match (11)	V <sub>OUT</sub> - V <sub>OUTMEAN</sub>	_	0.5	1.0	%	2.7V ≤	$V_{DD} \le 5.5V^{(2)}$			
	/V <sub>OUTMEAN</sub>	_	_	1.2	%	1.8V <sup>(2</sup>				
V <sub>OUT</sub> Tempco (see B.19 "V <sub>OUT</sub> Temperature Coefficient")	ΔV <sub>OUT</sub> /ΔT	_ 15 _			ppm/°C	Code = Mid-scale (7Fh, 1FFh or 7FFh)				
V <sub>REF</sub> pin Input Voltage Range	V <sub>REF</sub>	V <sub>SS</sub>	_	V <sub>DD</sub>	V	1.8V ≤	V <sub>DD</sub> ≤ 5.5V <sup>(1)</sup>			

Note 1 This parameter is ensured by design.

Note 2 This parameter is ensured by characterization.

Note 7 Resistance is defined as the resistance between the V<sub>REF</sub> pin (mode VRxB:VRxA = '10') to V<sub>SS</sub> pin. For dual-channel devices (MCP48FEBX2), this is the effective resistance of the each resistor ladder. The resistance measurement is of the two resistor ladders measured in parallel.

Note 11 Variation of one output voltage to mean output voltage.

1												
DC Characteristics	Standard Operating Conditions (unless otherwise specified): Operating Temperature: $-40^{\circ}\text{C} \le T_A \le +125^{\circ}\text{C}$ (Extended) Unless otherwise noted, all parameters apply across these specified operating ranges: $V_{DD} = +2.7\text{V}$ to 5.5V, $V_{REF} = +2.048\text{V}$ to $V_{DD}$ , $V_{SS} = 0\text{V}$ Gx = '0', $R_L = 5$ k $\Omega$ from $V_{OUT}$ to $V_{SS}$ , $C_L = 100$ pF Typical specifications represent values for $V_{DD} = 5.5\text{V}$ , $T_A = +25^{\circ}\text{C}$ .											
Parameters	Sym.	Min.	Min. Typ. Max. Units Conditions									
Zero-Scale Error (see <b>B.5</b>	E <sub>ZS</sub>	_	_	0.75	LSb	8-bit	VRxB:VRxA = '11', Gx = '0' V <sub>REF</sub> = V <sub>DD</sub> , No Load					
"Zero-Scale Error (EZS)")		Perfor	mance C	"Typical urves" <sup>(2)</sup>	LSb		VRxB:VRxA = '00', Gx = '0' V <sub>DD</sub> = 5.5V, No Load					
(Code = 000h)				"Typical urves" <sup>(2)</sup>	LSb		V <sub>DD</sub> = 1.8V, V <sub>REF</sub> = 1.0V VRxB:VRxA = '10', Gx = '0', No Load					
		Perfor	mance C	"Typical urves" <sup>(2)</sup>	LSb		V <sub>DD</sub> = 1.8V, V <sub>REF</sub> = 1.0V VRxB:VRxA = '11', Gx = '0', No Load					
				"Typical urves" <sup>(2)</sup>	LSb		VRxB:VRxA = '01', Gx = '0', No Load					
		_	_	3	LSb	10-bit	VRxB:VRxA = '11', Gx = '0' V <sub>REF</sub> = V <sub>DD</sub> , No Load					
		Perfor	mance C	"Typical urves" <sup>(2)</sup>	LSb		VRxB:VRxA = '00', Gx = '0' V <sub>DD</sub> = 5.5V, No Load					
		Perfor	mance C	"Typical urves" <sup>(2)</sup>	LSb		V <sub>DD</sub> = 1.8V, V <sub>REF</sub> = 1.0V VRxB:VRxA = '10', Gx = '0', No Load					
		Perfor	mance C	"Typical urves" <sup>(2)</sup>	LSb		V <sub>DD</sub> = 1.8V, V <sub>REF</sub> = 1.0V VRxB:VRxA = '11', Gx = '0', No Load					
				"Typical urves" <sup>(2)</sup>	LSb		VRxB:VRxA = '01', Gx = '0' No Load					
		_	_	12	LSb	12-bit	VRxB:VRxA = '11', Gx = '0' V <sub>REF</sub> = V <sub>DD</sub> , No Load					
		Perfor	mance C	"Typical urves" <sup>(2)</sup>	LSb		VRxB:VRxA = '00', Gx = '0' V <sub>DD</sub> = 5.5V, No Load					
		Perfor	mance C	"Typical urves" <sup>(2)</sup>	LSb		V <sub>DD</sub> = 1.8V, V <sub>REF</sub> = 1.0V VRxB:VRxA = '10', Gx = '0', No Load					
		Perfor	mance C	"Typical urves" <sup>(2)</sup>	LSb		V <sub>DD</sub> = 1.8V, V <sub>REF</sub> = 1.0V VRxB:VRxA = '11', Gx = '0', No Load					
				"Typical urves" <sup>(2)</sup>	LSb		VRxB:VRxA = '01', Gx = '0' No Load					
Offset Error (see B.7 "Offset Error (EOS)")	Eos	-15	±1.5	+15	mV	VRxB:V Gx = '0' No Load						
Offset Voltage Temperature Coefficient	V <sub>OSTC</sub>	_	±10	_	μV/°C							

Note 2 This parameter is ensured by characterization.

DC Characterist	ics	Standard Operating Conditions (unless otherwise specified): Operating Temperature: $-40^{\circ}\text{C} \le T_A \le +125^{\circ}\text{C}$ (Extended) Unless otherwise noted, all parameters apply across these specified operating ranges: $V_{DD} = +2.7\text{V}$ to $5.5\text{V}$ , $V_{REF} = +2.048\text{V}$ to $V_{DD}$ , $V_{SS} = 0\text{V}$ Gx = '0', $R_L = 5$ k $\Omega$ from $V_{OUT}$ to GND, $C_L = 100$ pF Typical specifications represent values for $V_{DD} = 5.5\text{V}$ , $T_A = +25^{\circ}\text{C}$ .									
Parameters	Sym.	Min.	Тур.	Max.	Units		Conditions				
Full-Scale Error (see <b>B.4</b>	E <sub>FS</sub>	_	_	4.5	LSb	8-bit	Code = FFh, VRxB:VRxA = '11' Gx = '0', V <sub>REF</sub> = 2.048V, No Load				
"Full-Scale Error (EFS)")			e Section 2.0 "T rformance Curv		LSb		Code = FFh, VRxB:VRxA = '10' Gx = '0', V <sub>REF</sub> = 2.048V, No Load				
			e Section 2.0 "T rformance Curv		LSb		Code = FFh, VRxB:VRxA = '01' Gx = '0', V <sub>REF</sub> = 2.048V, No Load				
			e Section 2.0 "T rformance Curv			Code = FFh, VRxB:VRxA = '00' No Load					
		_	_	18	LSb	10-bit	Code = 3FFh, VRxB:VRxA = '11' Gx = '0', V <sub>REF</sub> = 2.048V, No Load				
			e Section 2.0 "T rformance Curv		LSb		Code = 3FFh, VRxB:VRxA = '10' Gx = '0', V <sub>REF</sub> = 2.048V, No Load				
			e Section 2.0 "T rformance Curv		LSb		Code = 3FFh, VRxB:VRxA = '01' Gx = '0', V <sub>REF</sub> = 2.048V, No Load				
			e Section 2.0 "T rformance Curv		LSb		Code = 3FFh, VRxB:VRxA = '00' No Load				
		_	_	70	LSb	12-bit	Code = FFFh, VRxB:VRxA = '11' Gx = '0', V <sub>REF</sub> = 2.048V, No Load				
			e Section 2.0 "T rformance Curv		LSb		Code = FFFh, VRxB:VRxA = '10' Gx = '0', V <sub>REF</sub> = 2.048V, No Load				
			e Section 2.0 "T rformance Curv		LSb		Code = FFFh, VRxB:VRxA = '01' Gx = '0', V <sub>REF</sub> = 2.048V, No Load				
			e Section 2.0 "Tr rformance Curv		LSb		Code = FFFh, VRxB:VRxA = '00' No Load				

Note 2 This parameter is ensured by characterization.

DC Characteristics	Standard Operating Conditions (unless otherwise specified): Operating Temperature: $-40^{\circ}C \le T_A \le +125^{\circ}C$ (Extended) Unless otherwise noted, all parameters apply across these specified operating ranges: $V_{DD} = +2.7V$ to $5.5V$ , $V_{REF} = +2.048V$ to $V_{DD}$ , $V_{SS} = 0V$ Gx = '0', $R_L = 5$ k $\Omega$ from $V_{OUT}$ to GND, $C_L = 100$ pF Typical specifications represent values for $V_{DD} = 5.5V$ , $T_A = +25^{\circ}C$ .									
Parameters	Sym. Min. Typ. Max. Units Conditions									
Gain Error (see B.9 "Gain Error (EG)") <sup>(8)</sup>	E <sub>G</sub>	-1.0	±0.1	+1.0	% of FSR	8-bit	Code = 250, No Load VRxB:VRxA = '00' Gx = '0'			
		-1.0	±0.1	+1.0	% of FSR	10-bit	Code = 1000, No Load VRxB:VRxA = '00' Gx = '0'			
		-1.0	±0.1	+1.0	% of FSR	12-bit	Code = 4000, No Load VRxB:VRxA = '00' Gx = '0'			
Gain-Error Drift (see B.10 "Gain-Error Drift (EGD)")	∆G/°C	_	-3	_	ppm/°C					

**Note 2** This parameter is ensured by characterization.

Note 8 This gain error does not include offset error.

DC Characteristics		Standard Operating Conditions (unless otherwise specified):  Operating Temperature: $-40^{\circ}\text{C} \le T_{A} \le +125^{\circ}\text{C}$ (Extended)  Unless otherwise noted, all parameters apply across these specified operating ranges: $V_{DD} = +2.7V$ to 5.5V, $V_{REF} = +2.048V$ to $V_{DD}$ , $V_{SS} = 0V$ $Gx = '0'$ , $R_{L} = 5 \text{ k}\Omega$ from $V_{OUT}$ to GND, $C_{L} = 100 \text{ pF}$ Typical specifications represent values for $V_{DD} = 5.5V$ , $T_{A} = +25^{\circ}\text{C}$ .										
Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions						
Integral Nonlinearity (see B.11 "Integral Nonlinearity	INL	-0.5	±0.1	+0.5	LSb	8-bit	VRxB:VRxA = '10' (codes: 6 to 250) V <sub>DD</sub> = V <sub>REF</sub> = 5.5V					
(INL)") (10)		See Se Perform	ection 2.0 ' mance Cu	rypical rves" <sup>(2)</sup>	LSb		VRxB:VRxA = '00', '01', '11'					
			ction 2.0 ' nance Cu		LSb		VRxB:VRxA = '01' V <sub>DD</sub> = 5.5V, Gx = '1'					
		Perform	ction 2.0 ' nance Cu	rves" <sup>(2)</sup>	LSb		VRxB:VRxA = '10', '11' V <sub>REF</sub> = 1.0V, Gx = '1'					
		Perforr	ection 2.0 "Typical mance Curves" <sup>(2)</sup>		LSb		$V_{DD} = 1.8V$ $V_{REF} = 1.0V$					
		-1.5	±0.4	+1.5	LSb	10-bit	VRxB:VRxA = '10' (codes: 25 to 1000) V <sub>DD</sub> = V <sub>REF</sub> = 5.5V					
			ction 2.0 ' nance Cu		LSb		VRxB:VRxA = '00', '01', '11'					
		Perforr	ction 2.0 ' mance Cu	rves" <sup>(2)</sup>	LSb		VRxB:VRxA = '01' V <sub>DD</sub> = 5.5V, Gx = '1'					
		Perform	ction 2.0 ' mance Cu	rves" <sup>(2)</sup>	LSb		VRxB:VRxA = '10', '11' V <sub>REF</sub> = 1.0V, Gx = '1'					
			ction 2.0 ' nance Cu		LSb		V <sub>DD</sub> = 1.8V V <sub>REF</sub> = 1.0V					
		-6	±1.5	+6	LSb	12-bit	VRxB:VRxA = '10' (codes: 100 to 4000) V <sub>DD</sub> = V <sub>REF</sub> = 5.5V.					
		Perfor	ction 2.0 ' mance Cu	rves" <sup>(2)</sup>	LSb		VRxB:VRxA = '00', '01', '11'					
		Perfor	ction 2.0 ' mance Cu	rves" <sup>(2)</sup>	LSb		VRxB:VRxA = '01' V <sub>DD</sub> = 5.5V, Gx = '1'					
		Perfor	ction 2.0 ' mance Cu	rves" <sup>(2)</sup>	LSb		VRxB:VRxA = '10', '11' V <sub>REF</sub> = 1.0V, Gx = '1'					
			ction 2.0 ' mance Cu		LSb		V <sub>DD</sub> = 1.8V V <sub>REF</sub> = 1.0V					

Note 2 This parameter is ensured by characterization.

Note 10 Code range dependent on resolution: 8-bit, codes 6 to 250; 10-bit, codes 25 to 1000; 12-bit, codes 100 to 4000.

DC Characteristics		Standard Operating Conditions (unless otherwise specified): Operating Temperature: $-40^{\circ}\text{C} \le T_{A} \le +125^{\circ}\text{C}$ (Extended) Unless otherwise noted, all parameters apply across these specified operating ranges: $V_{DD} = +2.7 \text{V}$ to $5.5 \text{V}$ , $V_{REF} = +2.048 \text{V}$ to $V_{DD}$ , $V_{SS} = 0 \text{V}$ Gx = '0', $V_{CD} = 5.6 \text{V}$ from $V$									
Parameters	Sym.	Min. Typ. Max. Units Conditions									
Differential	DNL	-0.25	±0.0125	+0.25	LSb	8-bit	VRxB:VRxA = '10'				
Nonlinearity (see B.12							(codes: 6 to 250) V <sub>DD</sub> = V <sub>REF</sub> = 5.5V				
"Differential		See Se	ction 2.0	"Typical	LSb		Char: VRxB:VRxA = '00', '01', '11'				
Nonlinearity		Perfori	mance Cu	rves" <sup>(2)</sup>			G. G				
(DNL)") <sup>(10)</sup>		See Se	ction 2.0	"Typical	LSb		Char: VRxB:VRxA = '01'				
			mance Cu		1.01		$V_{DD} = 5.5V, Gx = '1'$				
			ction 2.0 mance Cu		LSb		Char: VRxB:VRxA = '10', '11' V <sub>REF</sub> = 1.0V, Gx = '1'				
			ction 2.0		LSb		V <sub>DD</sub> = 1.8V				
			mance Cu								
		-0.5	±0.05	+0.5	LSb	10-bit	VRxB:VRxA = '10'				
							(codes: 25 to 1000)				
		Coo Co	ction 2.0	"Tunical	LSb		V <sub>DD</sub> = V <sub>REF</sub> = 5.5V Char: VRxB:VRxA = '00', '01', '11'				
		Perfori	mance Cu	rves" <sup>(2)</sup>							
			ction 2.0		LSb		Char: VRxB:VRxA = '01'				
			mance Cu		1.01		V <sub>DD</sub> = 5.5V, Gx = '1'				
			ction 2.0 mance Cu		LSb		Char: VRxB:VRxA = '10', '11' V <sub>REF</sub> = 1.0V, Gx = '1'				
			ction 2.0		LSb		V <sub>DD</sub> = 1.8V				
			mance Cu		LOD		V <sub>DD</sub> = 1.0 V				
		-1.0	±0.2	+1.0	LSb	12-bit	VRxB:VRxA = '10'				
							(codes: 100 to 4000) V <sub>DD</sub> = V <sub>REF</sub> = 5.5V				
		See Se	ction 2.0	"Typical	LSb		Char: VRxB:VRxA = '00', '01', '11'				
		Perform	mance Cu	rves" <sup>(2)</sup>							
			ction 2.0 mance Cu		LSb		Char: VRxB:VRxA = '01' V <sub>DD</sub> = 5.5V, Gx = '1'				
			ction 2.0 mance Cu		LSb		Char: VRxB:VRxA = '10', '11' V <sub>REF</sub> = 1.0V, Gx = '1'				
			ction 2.0 mance Cu		LSb		V <sub>DD</sub> = 1.8V				

**Note 2** This parameter is ensured by characterization.

Note 10 Code range dependent on resolution: 8-bit, codes 6 to 250; 10-bit, codes 25 to 1000; 12-bit, codes 100 to 4000.

DC Characteristics	Operating Te Unless other V <sub>DD</sub> = +2.7V Gx = '0', R <sub>L</sub>	Standard Operating Conditions (unless otherwise specified): Operating Temperature: $-40^{\circ}C \le T_A \le +125^{\circ}C$ (Extended) Unless otherwise noted, all parameters apply across these specified operating ranges: $V_{DD} = +2.7V$ to $5.5V$ , $V_{REF} = +2.048V$ to $V_{DD}$ , $V_{SS} = 0V$ $Gx = '0'$ , $R_L = 5$ k $\Omega$ from $V_{OUT}$ to GND, $C_L = 100$ pF Typical specifications represent values for $V_{DD} = 5.5V$ , $T_A = +25^{\circ}C$ .										
Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions						
-3 dB Bandwidth (see B.16 "-3 dB Bandwidth")	BW		200	_	kHz kHz	V <sub>REF</sub> = 2.048V ± 0.1V VRxB:VRxA = '10', Gx = '0' V <sub>RFF</sub> = 2.048V ± 0.1V						
,			100			VRxB:VRxA = '10', Gx = '1'						
Output Amplifier	l											
Minimum Output Voltage	V <sub>OUT(MIN)</sub>		0.01	_	<b>V</b>	$ \begin{array}{l} 1.8V \leq V_{DD} < 5.5V \\ Output \ Amplifier's \ minimum \ drive \end{array} $						
Maximum Output Voltage	V <sub>OUT(MAX)</sub>		V <sub>DD</sub> – 0.04	_	>	1.8V ≤ V <sub>DD</sub> < 5.5V Output Amplifier's maximum drive						
Phase Margin	PM		66	_	Degree (°)	C <sub>L</sub> = 400 pF R <sub>L</sub> = ∞						
Slew Rate (9)	SR		0.44	_	V/µs	$R_L = 5 k\Omega$						
Short-Circuit Current	I <sub>SC</sub>	3	9	14	mA	DAC code = Full Scale						
Internal Band Gap												
Band Gap Voltage	$V_{BG}$	1.18	1.22	1.26	V							
Band Gap Voltage Temperature Coefficient	V <sub>BGTC</sub>	_	15	_	ppm/°C							
Operating Range		2.0	_	5.5	V	V <sub>REF</sub> pin voltage stable						
(V <sub>DD</sub> )		2.2	_	5.5	V	V <sub>OUT</sub> output linear						
External Reference (V												
Input Range (1)	$V_{REF}$	$V_{SS}$	_	$V_{DD} - 0.04$	V	VRxB:VRxA = '11' (Buffered mode)						
		$V_{SS}$	_	$V_{DD}$	V	VRxB:VRxA = '10' (Unbuffered mode)						
Input Capacitance	C <sub>REF</sub>		1	_	pF	VRxB:VRxA = '10' (Unbuffered mode)						
Total Harmonic Distortion <sup>(1)</sup>	THD	ı	-64	_	dB	V <sub>REF</sub> = 2.048V ± 0.1V VRxB:VRxA = '10', Gx = '0' Frequency = 1 kHz						
Dynamic Performance	e											
Major Code Transition Glitch (see B.14 "Major-Code Transition Glitch")		_	45	_	nV-s	1 LSb change around major carry (7FFh to 800h)						
Digital Feedthrough (see B.15 "Digital Feed-through")			<10		nV-s							

Note 1 This parameter is ensured by design.

Note 9 Within 1/2 LSb of final value when code changes from 1/4 to 3/4 of FSR. (Example: 400h to C00h in 12-bit device).

DC Characteristics	Standard Operating Conditions (unless otherwise specified): Operating Temperature: $-40^{\circ}\text{C} \le T_{A} \le +125^{\circ}\text{C}$ (Extended) Unless otherwise noted, all parameters apply across these specified operating ranges: $V_{DD} = +2.7\text{V}$ to $5.5\text{V}$ , $V_{REF} = +2.048\text{V}$ to $V_{DD}$ , $V_{SS} = 0\text{V}$ Gx = '0', $R_{L} = 5 \text{ k}\Omega$ from $V_{OUT}$ to GND, $C_{L} = 100 \text{ pF}$ Typical specifications represent values for $V_{DD} = 5.5\text{V}$ , $T_{A} = +25^{\circ}\text{C}$ .										
Parameters	Sym.	Sym. Min. Typ. Max. Units Conditions									
Digital Inputs/Outputs (CS, SCK, SDI, SDO, LAT0/HVC)											
Schmitt Trigger	V <sub>IH</sub>	0.45 V <sub>DD</sub>	_	_	V	$2.7V \le V_{DD} \le 5.5V$					
High-Input Threshold		0.5 V <sub>DD</sub>	_		V	$1.8V \le V_{DD} \le 2.7V$					
Schmitt Trigger Low-Input Threshold	V <sub>IL</sub>	_	_	0.2 V <sub>DD</sub>	V						
Hysteresis of Schmitt Trigger Inputs	V <sub>HYS</sub>	_	0.1 V <sub>DD</sub>	_	V						
Output Low Voltage	$V_{OL}$	$V_{SS}$	_	$0.3V_{DD}$	V	I <sub>OL</sub> = 5 mA, V <sub>DD</sub> = 5.5V					
		$V_{SS}$	_	$0.3V_{DD}$	V	I <sub>OL</sub> = 1 mA, V <sub>DD</sub> = 1.8V					
Output High Voltage	V <sub>OH</sub>	0.7V <sub>DD</sub>	_	$V_{DD}$	٧	I <sub>OH</sub> = -2.5 mA, V <sub>DD</sub> = 5.5V					
	$0.7V_{DD}$ — $V_{DD}$ V $I_{OH}$ = -1 mA, $V_{DD}$ = 1.8V										
Input Leakage Current	I <sub>IL</sub>	-1	_	1	μΑ	$V_{IN} = V_{DD}$ and $V_{IN} = V_{SS}$					
Pin Capacitance	C <sub>IN</sub> , C <sub>OUT</sub>	_	10	_	pF	f <sub>C</sub> = 20 MHz					

DC Characteristics	Operating Unless of V <sub>DD</sub> = +2 Gx = '0',	g Temperatherwise not $0.7V$ to $5.5V$ $R_L = 5 k\Omega$	rating Conditions (unless otherwise specified): perature: $-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$ (Extended) se noted, all parameters apply across these specified operating ranges: $0.5.5\text{V}, \text{V}_{\text{REF}} = +2.048\text{V}$ to $\text{V}_{\text{DD}}, \text{V}_{\text{SS}} = 0\text{V}$ $0.56 \text{K}\Omega$ from $\text{V}_{\text{OUT}}$ to GND, $\text{C}_{\text{L}} = 100 \text{ pF}$ cations represent values for $\text{V}_{\text{DD}} = 5.5\text{V}, \text{T}_{\text{A}} = +25^{\circ}\text{C}$ .							
Parameters	Sym.	Min.	Тур.	Max.	Units		Conditions			
RAM Value	RAM Value									
Value Range	N	0h		FFh	hex	8-bit				
		0h	1	3FFh	hex	10-bit				
		0h		FFFh	hex	12-bit				
DAC Register	N	Se	e Table 4	-2	hex	8-bit				
POR/BOR Value		Se	e Table 4	-2	hex	10-bit				
		Se	e Table 4	-2	hex	12-bit				
PDCON Initial		See Table 4-2 hex								
Factory Setting										
EEPROM	1				1	1				
Endurance	EN <sub>EE</sub>		1M	_	Cycles	Note 1,				
Data Retention	DR <sub>EE</sub>		200		Years		C (1), ( 2)			
EEPROM Range	N	0h	_	FFh	hex	8-bit	DACx Register(s)			
		0h	_	3FFh	hex	10-bit	DACx Register(s)			
		0h	_	FFFh	hex	12-bit	DACx Register(s)			
Initial Factory Setting	N	Se	e Table 4	-2						
EEPROM Programming Write Cycle Time	t <sub>WC</sub>	_	11	16	16 ms $V_{DD} = +1.8V \text{ to } 5.5V$					
Power Requirements										
Power Supply Sensitivity	PSS	_	0.002	0.005	%/%	8-bit	Code = 7Fh			
(B.17 "Power-Supply		_	0.002	0.005	%/%	10-bit	Code = 1FFh			
Sensitivity (PSS)")		_	0.002	0.005	%/%	12-bit	Code = 7FFh			

Note 1 This parameter is ensured by design.

Note 2 This parameter is ensured by characterization.

#### DC Notes:

- 1. This parameter is ensured by design.
- 2. This parameter is ensured by characterization.
- 3. POR/BOR voltage trip point is not slope dependent. Hysteresis implemented with time delay.
- 4. Supply current is independent of current through the resistor ladder in mode VRxB:VRxA = '10'.
- 5. The PDxB:PDxA = '01', '10', and '11' configurations should have the same current.
- 6. By design, this is the worst-case current mode.
- Resistance is defined as the resistance between the V<sub>REF</sub> pin (mode VRxB:VRxA = '10') to V<sub>SS</sub> pin. For dual-channel devices (MCP48FEBX2), this is the effective resistance of the each resistor ladder. The resistance measurement is of the two resistor ladders measured in parallel.
- 8. This gain error does not include offset error.
- 9. Within 1/2 LSb of final value when code changes from 1/4 to 3/4 of FSR. (Example: 400h to C00h in 12-bit device).
- 10. Code range dependent on resolution: 8-bit, codes 6 to 250; 10-bit, codes 25 to 1000; 12-bit, codes 100 to 4000.
- 11. Variation of one output voltage to mean output voltage.

### 1.1 Reset, Power-Down, and SPI Mode Timing Waveforms and Requirements

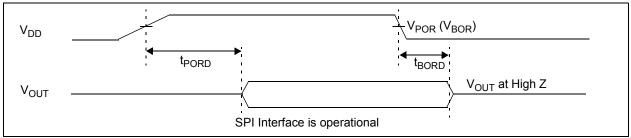


FIGURE 1-1: Power-on and Brown-out Reset Waveforms.

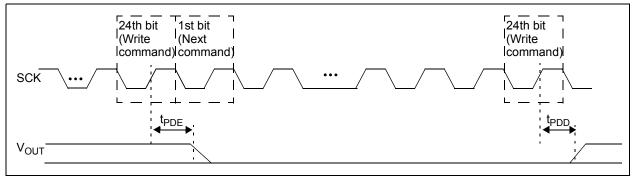


FIGURE 1-2: SPI Power-Down Command Waveforms.

TABLE 1-1: RESET AND POWER-DOWN TIMING

Timing Characteristics	<b>3</b>	Opera Unles V <sub>DD</sub> = R <sub>L</sub> =	ating T s other = +1.8\ 5 kΩ fr	emperatives of the two sections of the twide two sections of the two sections of the two sections of the t	ature: -4 oted, all 5V, V <sub>SS</sub> <sub>UT</sub> to V	conditions (unless otherwise specified): $-40^{\circ}\text{C} \le T_{A} \le +125^{\circ}\text{C}$ (Extended) all parameters apply across these specified operating ranges: $S_{SS} = 0\text{V}$ $V_{SS}$ , $C_{L} = 100 \text{ pF}$ expresent values for $V_{DD} = 5.5\text{V}$ , $T_{A} = +25^{\circ}\text{C}$ .				
Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions				
Power-on Reset Delay	t <sub>PORD</sub>	_	60	_	μs					
Brown-out Reset Delay	t <sub>BORD</sub>	_	45		μs	$V_{DD}$ transitions from $V_{DD(MIN)} \rightarrow V_{POR}$ $V_{OUT}$ driven to $V_{OUT}$ disabled				
Power-Down Output Disable Time Delay	T <sub>PDD</sub>	_	10.5		μs	PDxB:PDxA = '11', '10', or '01' $\rightarrow$ "00" started from falling edge of the SCK at the end of the 24th clock cycle. Volatile DAC Register = FFh, $V_{OUT}$ = 10 mV. $V_{OUT}$ not connected.				
Power-Down Output Enable Time Delay	T <sub>PDE</sub>	_	1		μs	PDxB:PDxA = "00" $\rightarrow$ '11', '10', or '01' started from falling edge of the SCK at the end of the 24th clock cycle. $V_{OUT} = V_{OUT} - 10$ mV. $V_{OUT}$ not connected.				

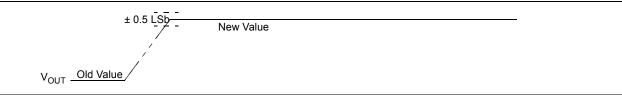


FIGURE 1-3: V<sub>OUT</sub> Settling Time Waveform.

TABLE 1-2: V<sub>OUT</sub> SETTLING TIMING

Timing Characteristi	cs	Operat Unless V <sub>DD</sub> = R <sub>L</sub> = 5	ing Tem otherwis +1.8V to kΩ from	perature se noted, 5.5V, V 1 V <sub>OUT</sub> to	e: -40°C all parai s <sub>SS</sub> = 0V o V <sub>SS</sub> , C	$\leq$ T <sub>A</sub> $\leq$ + meters a $\alpha$	ess otherwise specified): 125°C (Extended) pply across these specified operating ranges:  pF for V <sub>DD</sub> = 5.5V, T <sub>A</sub> = +25°C.	
Parameters	Sym.	Min.	Тур.	Max.	Units		Conditions	
V <sub>OUT</sub> Settling Time	t <sub>S</sub>	_	7.8	_	μs	8-bit	Code = $40h \rightarrow C0h$ ; $C0h \rightarrow 40h$ (3)	
(±0.5LSb error band,		_	7.8	_	μs	10-bit	Code = $100h \rightarrow 300h$ ; $300h \rightarrow 100h$ (3)	
C <sub>L</sub> = 100 pF) (see <b>B.13 "Settling</b> <b>Time"</b> )			7.8		μs	12-bit Code = 400h $\rightarrow$ C00h; C00h $\rightarrow$ 400h (3)		

Note 3 Within 1/2 LSb of final value when code changes from 1/4 to 3/4 of FSR. (Example: 400h to C00h in 12-bit device).

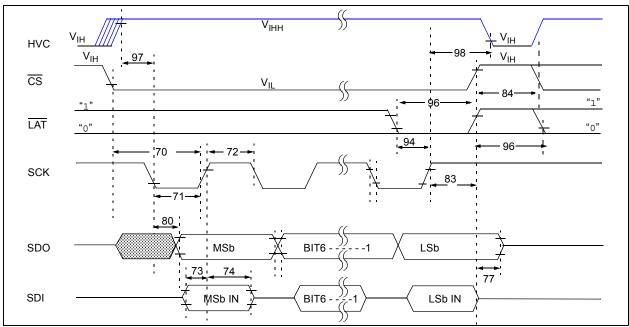


FIGURE 1-4: SPI Timing (Mode = 11) Waveforms.

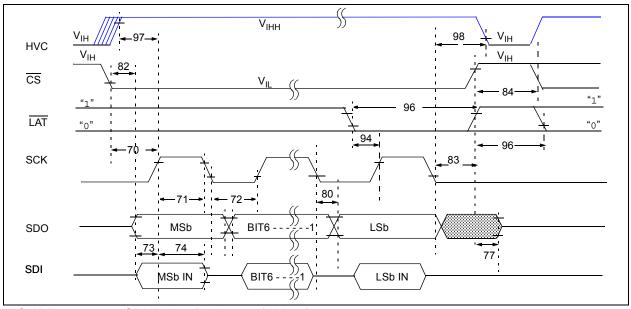


FIGURE 1-5: SPI Timing (Mode = 00) Waveforms.

TABLE 1-3: SPI REQUIREMENTS (MODE = 11)

SPI AC	Characteris	itics	Standard Operating Conditions (unless otherwise specified): Operating Temperature: $-40^{\circ}C \le T_A \le +125^{\circ}C$ (Extended) Operating Voltage range is described in DC Characteristics.						
Param. No.	Symbol		Characteristic	Min.	Max.	Units	Conditions		
	F <sub>SCK</sub>	SCK input free	quency	_	10	MHz	V <sub>DD</sub> = 2.7V to 5.5V (Read Command)		
				_	20	MHz	V <sub>DD</sub> = 2.7V to 5.5V (All Other Commands)		
				_	1	MHz	$V_{DD}$ = 1.8V to 2.7V		
70	TcsA2scH	CS Active (V <sub>IL</sub>	) to command's 1st SCK↑ input	60	_	ns			
71	TscH	SCK input high	h time	20	_	ns	$V_{DD} = 2.7V \text{ to } 5.5V$		
				400	_	ns	$V_{DD}$ = 1.8V to 2.7V		
72	TscL	SCK input low	time	20	_	ns	$V_{DD}$ = 2.7V to 5.5V		
				400	_	ns	$V_{DD}$ = 1.8V to 2.7V		
73	TdiV2scH	Setup time of SDI input to SCK↑ edge			_	ns			
74	TscH2diL	Hold time of S	DI input from SCK↑ edge	20	_	ns			
77	TcsH2DoZ	CS Inactive (V	IH) to SDO output hi-impedance	_	50	ns	Note 1		
80	TscL2doV	SDO data out	out valid after SCK↓ edge	_	45	ns	$V_{DD} = 2.7V \text{ to } 5.5V$		
				_	170	ns	V <sub>DD</sub> = 1.8V to 2.7V		
83	TscH2csL	CS Inactive (V	′ <sub>IH</sub> ) after SCK↑ edge	100	_	ns	V <sub>DD</sub> = 2.7V to 5.5V		
				1		μs	V <sub>DD</sub> = 1.8V to 2.7V		
84	TcsH	CS high time (	(V <sub>IH</sub> )	50	_	ns			
94	T <sub>LATSU</sub>	LAT ↓ to SCK	(write data 24th bit) setup time	20	_	ns	Write Data transferred (4)		
96	T <sub>LAT</sub>	LAT high or lo	w time	20	_	ns			
97	T <sub>HVCSU</sub>	HVC ↑ to SCK ↓ (1st data bit) (HVC setup time)			_	ns	High-Voltage Commands <sup>(1)</sup>		
98	T <sub>HVCHD</sub>	SCK ↑ (last bi to HVC ↓ (HV	t of command (8th or 24th bit)) C hold time)	25	_	ns	High-Voltage Commands <sup>(1)</sup>		

Note 1 This parameter is ensured by design.

Note 4 The transition of the LAT signal must occur 10 ns before the rising edge of the 24th SCK signal (Spec 94) or the current register data value may not be transferred to the output latch (VOUT) before the register is overwritten with the new value.

TABLE 1-4: SPI REQUIREMENTS (MODE = 00)

SPI AC	Characteris	tics	Standard Operating Conditions (unless otherwise specified): Operating Temperature: $-40^{\circ}\text{C} \le T_{A} \le +125^{\circ}\text{C}$ (Extended) Operating Voltage range is described in DC Characteristics.						
Param. No.	Sym.	Ch	aracteristic	Min.	Max.	Units	Conditions		
	F <sub>SCK</sub>	SCK input frequen	су		10	MHz	V <sub>DD</sub> = 2.7V to 5.5V (Read Command)		
				_	20	MHz	V <sub>DD</sub> = 2.7V to 5.5V (All Other Commands)		
					1	MHz	$V_{DD} = 1.8V \text{ to } 2.7V$		
70		CS Active (V <sub>IL</sub> ) to		60	_	ns			
71	TscH	SCK input high tim	е	20	_	ns	$V_{DD} = 2.7V \text{ to } 5.5V$		
				400	_	ns	$V_{DD}$ = 1.8V to 2.7V		
72	TscL	SCK input low time			_	ns	$V_{DD}$ = 2.7V to 5.5V		
				400	_	ns	$V_{DD}$ = 1.8V to 2.7V		
73	TDIV2scH	Setup time of SDI	input to SCK↑ edge	10	_	ns			
74	TscH2DIL	Hold time of SDI in	put from SCK↑ edge	20	_	ns			
77	TcsH2DoZ	CS Inactive (V <sub>IH</sub> ) to	SDO output hi-impedance	_	50	ns	Note 1		
80	TscL2DOV	SDO data output v	alid after SCK↓ edge	_	45	ns	$V_{DD} = 2.7V \text{ to } 5.5V$		
					170	ns	$V_{DD}$ = 1.8V to 2.7V		
82	TssL2doV	SDO data output v	alid after	1	70	ns			
83	TscH2csL	CS Inactive (V <sub>IH</sub> ) a	ıfter SCK↓ edge	100	_	ns	$V_{DD} = 2.7V \text{ to } 5.5V$		
				1		μs	$V_{DD}$ = 1.8V to 2.7V		
84	TcsH	CS high time (V <sub>IH</sub> )		50	_	ns			
94	T <sub>LATSU</sub>	LAT ↓ to SCK↑ (w	rite data 24th bit) setup time	10	_	ns	Write Data transferred (4)		
96	T <sub>LAT</sub>	LAT high or low tin	ne	50	_	ns			
97	T <sub>HVCSU</sub>	HVC ↑ to SCK ↑ (1st data bit) (HVC setup time)			_	ns	High-Voltage Commands <sup>(1)</sup>		
98	T <sub>HVCHD</sub>	SCK ↓ (last bit of control of the HVC ↓ (HVC hold	ommand (8th or 24th bit)) to time)	25	_	ns	High-Voltage Commands <sup>(1)</sup>		

Note 1 This parameter is ensured by design.

Note 4 The transition of the LAT signal must occur 10 ns before the rising edge of the 24th SCK signal (Spec 94) or the current register data value may not be transferred to the output latch (VOUT) before the register is overwritten with the new value.

### **Timing Table Notes:**

- 1. This parameter is ensured by design.
- 2. This parameter ensured by characterization.
- 3. Within 1/2 LSb of final value when code changes from 1/4 to 3/4 of FSR. (Example: 400h to C00h in 12-bit device).
- 4. The transition of the LAT signal must occur 10 ns before the rising edge of the 24th SCK signal (Spec 94) or the current register data value may not be transferred to the output latch (V<sub>OUT</sub>) before the register is overwritten with the new value.

### **Temperature Specifications**

Electrical Specifications: Unless otherwise indicated, V <sub>DD</sub> = +2.7V to +5.5V, V <sub>SS</sub> = GND.									
Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions			
Temperature Ranges									
Specified Temperature Range	T <sub>A</sub>	-40	_	+125	°C				
Operating Temperature Range	T <sub>A</sub>	-40	_	+125	°C	Note 1			
Storage Temperature Range	T <sub>A</sub>	-65	_	+150	°C				
Thermal Package Resistances									
Thermal Resistance, 10LD-MSOP	$\theta_{JA}$	_	202		°C/W				

Note 1: The MCP48FEBXX devices operate over this extended temperature range, but with reduced performance. Operation in this range must not cause  $T_J$  to exceed the Maximum Junction Temperature of +150°C.

#### 2.0 TYPICAL PERFORMANCE CURVES

Note:

The device Performance Curves are available in a separate document. This is done to keep the file size of this PDF document less than the 10 MB file attachment limit of many mail servers.

The MCP48FXBXX Performance Curves document is literature number **DS20005440**, and can be found on the Microchip website. Look on the MCP48FEBXX product page under "Documentation and Software", in the Data Sheets category.

NOTES:

#### 3.0 PIN DESCRIPTIONS

Overviews of the pin functions are provided in Sections 3.1 "Positive Power Supply Input (V<sub>DD</sub>)" through Section 3.10 "SPI - Serial Clock Pin (SCK)". The descriptions of the pins for the single-DAC output device are listed in Table 3-1, and descriptions for the dual-DAC output device are listed in Table 3-2.

TABLE 3-1: MCP48FEBX1 (Single-DAC) Pinout Description

MSOP-10LD Symbol I/O Buffer Type					
			Standard Function		
1	$V_{DD}$		Р	Supply Voltage Pin	
2	CS	ı	ST	SPI Chip Select Pin	
3	V <sub>REF0</sub>	Α	Analog	Voltage Reference Input Pin	
4	V <sub>OUT0</sub>	Α	Analog	Buffered Analog Voltage Output Pin	
5	NC	_	_	Not Internally Connected	
6	LAT0/HVC	_	HV ST	DAC Register Latch/High-Voltage Command Pin. Latch Pin allows the value in the Serial Shift Register to transfer to the volatile DAC register. High-Voltage command allows User Configuration Bits to be written.	
7	V <sub>SS</sub>	_	Р	Ground Reference Pin for all circuitries on the device	
8	SDO	0	_	SPI Serial Data Output Pin	
9	SCK	I	ST	SPI Serial Clock Pin	
10	SDI	I	ST	SPI Serial Data Input Pin	

**Legend:** A = Analog ST = Schmitt Trigger HV = High Voltage

I = Input O = Output I/O = Input/Output P = Power

TABLE 3-2: MCP48FEBX2 (Dual-DAC) Pinout Description

			(	to, i mout boomption
Pin				
MSOP-10LD Symbol I/O Buffer Type			Standard Function	
1	$V_{DD}$	_	Р	Supply Voltage Pin
2	CS	I	ST	SPI Chip Select Pin
3	$V_{REF}$	Α	Analog	Voltage Reference Input Pin (for DAC0 and DAC1)
4	V <sub>OUT0</sub>	Α	Analog	Buffered Analog Voltage Output 0 Pin
5	V <sub>OUT1</sub>	Α	Analog	Buffered Analog Voltage Output 1 Pin
6	LAT0/HVC	I	HV ST	DAC Register Latch/High-Voltage Command Pin. Latch Pin allows the value in the Serial Shift Register to transfer to the volatile DAC register (for DAC0 and DAC1). High-Voltage command allows User Configuration Bits to be written.
7	V <sub>SS</sub>	_	Р	Ground Reference Pin for all circuitries on the device
8	SDO	0	_	SPI Serial Data Output Pin
9	SCK	I	ST	SPI Serial Clock Pin
10	SDI	1	ST	SPI Serial Data Input Pin

**Legend:** A = Analog ST = Schmitt Trigger HV = High Voltage

I = Input O = Output I/O = Input/Output P = Power

#### 3.1 Positive Power Supply Input (V<sub>DD</sub>)

 $V_{DD}$  is the positive supply voltage input pin. The input supply voltage is relative to  $V_{SS}$ .

The power supply at the  $V_{DD}$  pin should be as clean as possible for a good DAC performance. It is recommended to use an appropriate bypass capacitor of about 0.1  $\mu$ F (ceramic) to ground. An additional 10  $\mu$ F capacitor (tantalum) in parallel is also recommended to further attenuate noise present in application boards.

#### 3.2 Voltage Reference Pin (V<sub>REF</sub>)

The  $V_{REF}$  pin is either an input or an output. When the DAC's voltage reference is configured as the  $V_{REF}$  pin, the pin is an input. When the DAC's voltage reference is configured as the internal band gap, the pin is an output.

When the DAC's voltage reference is configured as the  $V_{REF}$  pin, there are two options for this voltage input:

- · V<sub>REF</sub> pin voltage buffered
- V<sub>REF</sub> pin voltage unbuffered

The buffered option is offered in cases where the external reference voltage does not have sufficient current capability to not drop its voltage when connected to the internal resistor ladder circuit.

When the DAC's voltage reference is configured as the device  $V_{DD}$ , the  $V_{REF}$  pin is disconnected from the internal circuit.

When the DAC's voltage reference is configured as the internal band gap, the  $V_{REF}$  pin's drive capability is minimal, so the output signal should be buffered.

See Section 5.2 "Voltage Reference Selection" and Register 4-2 for more details on the configuration bits.

#### 3.3 Analog Output Voltage Pin (V<sub>OUT</sub>)

V<sub>OUT</sub> is the DAC analog voltage output pin. The DAC output has an output amplifier. The DAC output range is dependent on the selection of the voltage reference source (and potential Output Gain selection). These are:

- Device V<sub>DD</sub> The full-scale range of the DAC output is from V<sub>SS</sub> to approximately V<sub>DD</sub>.
- V<sub>REF</sub> pin The full-scale range of the DAC output is from V<sub>SS</sub> to G \* V<sub>RL</sub>, where G is the gain selection option (1x or 2x).
- Internal Band Gap The full-scale range of the DAC output is from V<sub>SS</sub> to G \* (2 \* V<sub>BG</sub>), where G is the gain selection option (1x or 2x).

In Normal mode, the DC impedance of the output pin is about  $1\Omega.$  In Power-Down mode, the output pin is internally connected to a known pull-down resistor of 1 k $\Omega,$  100 k $\Omega,$  or open. The Power-Down Selection bits settings are shown in Register 4-3 and Table 5-5.

#### 3.4 No Connect (NC)

The NC pin is not connected to the device.

#### 3.5 Ground $(V_{SS})$

The V<sub>SS</sub> pin is the device ground reference.

The user must connect the  $V_{SS}$  pin to a ground plane through a low-impedance connection. If an analog ground path is available in the application PCB (printed circuit board), it is highly recommended that the  $V_{SS}$  pin be tied to the analog ground path or isolated within an analog ground plane of the circuit board.

## 3.6 Latch Pin (LAT)/High-Voltage Command (HVC)

The LAT pin is used to force the transfer of the DAC register's shift register to the DAC output register. This allows DAC outputs to be updated at the same time.

The update of the VRxB:VRxA, PDxB:PDxA and Gx bits are also controlled by the LAT pin state.

The HVC pin allows the device's nonvolatile user configuration bits to be programmed when the HVC pin is greater than the  $V_{IHH}$  entry voltage.

### 3.7 SPI - Chip Select Pin (CS)

The CS pin enables/disables the serial interface. The serial interface must be enabled for the SPI commands to be received by the device.

Refer to Section 6.2 "SPI Serial Interface" for more details of SPI Serial Interface communication.

The NC pin is not connected to the device.

#### 3.8 SPI - Serial Data In Pin (SDI)

The SDI pin is the serial data input pin of the SPI interface. The SDI pin is used to read the DAC registers and configuration bits.

Refer to Section 6.2 "SPI Serial Interface" for more details of SPI Serial Interface communication.

#### 3.9 SPI - Serial Data Out Pin (SDO)

The SDO pin is the serial data output pin of the SPI interface. The SDO pin is used to write the DAC registers and configuration bits.

Refer to Section 6.2 "SPI Serial Interface" for more details of SPI Serial Interface communication.

#### 3.10 SPI - Serial Clock Pin (SCK)

The SCK pin is the serial clock pin of the SPI interface. The MCP48FEBXX SPI Interface only accepts external serial clocks.

Refer to Section 6.2, SPI Serial Interface for more details of SPI Serial Interface communication.

#### 4.0 GENERAL DESCRIPTION

The MCP48FEBX1 (MCP48FEB01, MCP48FEB11, and MCP48FEB21) devices are single-channel voltage output devices. The MCP48FEBX2 (MCP48FEB02, MCP48FEB12, and MCP48FEB22) devices are dual-channel voltage output devices.

These devices are offered with 8-bit (MCP48FEB0X), 10-bit (MCP48FEB1X) and 12-bit (MCP48FEB2X) resolution and include nonvolatile memory (EEPROM), an SPI serial interface and a write latch (LAT) pin to control the update of the written DAC value to the DAC output pin.

The devices use a resistor ladder architecture. The resistor ladder DAC is driven from a software-selectable voltage reference source. The source can be either the device's internal  $V_{DD}$ , an external  $V_{REF}$  pin voltage (buffered or unbuffered) or an internal band gap voltage source.

The DAC output is buffered with a low power and precision output amplifier (op amp). This output amplifier provides a rail-to-rail output with low offset voltage and low noise. The gain (1x or 2x) of the output buffer is software configurable.

This device also has user-programmable nonvolatile memory (EEPROM), which allows the user to save the desired POR/BOR value of the DAC register and device configuration bits. High-voltage lock bits can be used to ensure that the devices output settings are not accidentally modified.

The devices operate from a single supply voltage. This voltage is specified from 2.7V to 5.5V for full specified operation, and from 1.8V to 5.5V for digital operation. The devices operate between 1.8V and 2.7V, but some device parameters are not specified.

The main functional blocks are:

- Power-on Reset/Brown-out Reset (POR/BOR)
- Device Memory
- Resistor Ladder
- Output Buffer/V<sub>OUT</sub> Operation
- Internal Band Gap (Voltage Reference)
- SPI Serial Interface Module

## 4.1 Power-on Reset/Brown-out Reset (POR/BOR)

The internal Power-on Reset (POR)/Brown-out Reset (BOR) circuit monitors the power supply voltage ( $V_{DD}$ ) during operation. This circuit ensures correct device start-up at system power-up and power-down events. The device's RAM retention voltage ( $V_{RAM}$ ) is lower than the POR/BOR voltage trip point ( $V_{POR}/V_{BOR}$ ). The maximum  $V_{POR}/V_{BOR}$  voltage is less than 1.8V.

POR occurs as the voltage is rising (typically from 0V), while BOR occurs as the voltage is falling (typically from  $V_{DD(MIN)}$  or higher).

The POR and BOR trip points are at the same voltage, and the condition is determined by whether the  $V_{DD}$  voltage is rising or falling (see Figure 4-1). What occurs is different depending on whether the reset is a POR or BOR.

When  $V_{POR}/V_{BOR} < V_{DD} < 2.7V$ , the electrical performance may not meet the data sheet specifications. In this region, the device is capable of reading and writing to its EEPROM and reading and writing to its volatile memory if the proper serial command is executed.

#### 4.1.1 POWER-ON RESET

The Power-on Reset is the case where the device  $V_{DD}$  is having power applied to it from the  $V_{SS}$  voltage level. As the device powers up, the  $V_{OUT}$  pin will float to an unknown value. When the device's  $V_{DD}$  is above the transistor threshold voltage of the device, the output will start being pulled low. After the  $V_{DD}$  is above the POR/BOR trip point ( $V_{BOR}/V_{POR}$ ), the resistor network's wiper will be loaded with the POR value (mid-scale). The volatile memory determines the analog output ( $V_{OUT}$ ) pin voltage. After the device is powered-up, the user can update the device memory.

When the rising  $V_{DD}$  voltage crosses the  $V_{POR}$  trip point, the following occurs:

- Nonvolatile DAC register value is latched into volatile DAC register
- Nonvolatile configuration bit values are latched into volatile configuration bits
- POR Status bit is set ('1')
- The Reset Delay Timer (t<sub>PORD</sub>) starts; when the reset delay timer (t<sub>PORD</sub>) times out, the SPI serial interface is operational. During this delay time, the SPI interface will not accept commands.
- The Device Memory Address pointer is forced to non

The analog output (V<sub>OUT</sub>) state will be determined by the state of the volatile configuration bits and the DAC register. This is called a Power-on Reset (event).

Figure 4-1 illustrates the conditions for power-up and power-down events under typical conditions.

#### 4.1.2 BROWN-OUT RESET

The Brown-out Reset occurs when a device had power applied to it and that power (voltage) drops below the specified range.

When the falling  $V_{DD}$  voltage crosses the  $V_{POR}$  trip point (BOR event), the following occurs:

- · Serial Interface is disabled
- · EEPROM Writes are disabled
- Device is forced into a Power-Down state (PDxB:PDxA = '11'). Analog circuitry is turned off.
- · Volatile DAC Register is forced to 000h
- Volatile configuration bits VRxB:VRxA and Gx are forced to '0'

If the V<sub>DD</sub> voltage decreases below the V<sub>RAM</sub> voltage, all volatile memory may become corrupted.

As the voltage recovers above the V<sub>POR</sub>/V<sub>BOR</sub> voltage, see **Section 4.1.1 "Power-on Reset"**.

Serial commands not completed due to a brown-out condition may cause the memory location (volatile and nonvolatile) to become corrupted.

Figure 4-1 illustrates the conditions for power-up and power-down events under typical conditions.

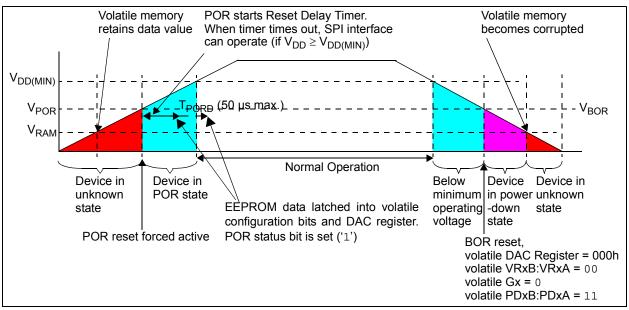


FIGURE 4-1: Power-on Reset Operation.

#### 4.2 Device Memory

User memory includes three types of memory:

- Volatile Register Memory (RAM)
- Nonvolatile Register Memory
- Device Configuration Memory

Each memory address is 16 bits wide. There are five nonvolatile user-control bits that do not reside in memory mapped register space (see Section 4.2.3 "Device Configuration Memory").

## 4.2.1 VOLATILE REGISTER MEMORY (RAM)

There are up to six volatile memory locations:

- · DAC0 and DAC1 Output Value Registers
- · VREF Select Register
- · Power-Down Configuration Register
- · Gain and Status Register
- · WiperLock Technology Status Register

The volatile memory starts functioning when the device  $V_{DD}$  is at (or above) the RAM retention voltage ( $V_{RAM}$ ). The volatile memory will be loaded with the default device values when the  $V_{DD}$  rises across the  $V_{POR}/V_{BOR}$  voltage trip point.

TABLE 4-1: MEMORY MAP (x16)

Address	Function	Config Bit <sup>(1)</sup>
00h	Volatile DAC0 Register	CL0
01h	Volatile DAC1 Register	CL1
02h	Reserved	
03h	Reserved	
04h	Reserved	
05h	Reserved	
06h	Reserved	
07h	Reserved	
08h	V <sub>REF</sub> Register	
09h	Power-Down Register	
0Ah	Gain and Status Register	
0Bh	WiperLock™ Technology Status Register	
0Ch	Reserved	_
0Dh	Reserved	_
0Eh	Reserved	_
0Fh	Reserved	_

Volatile Memory address range

4.2.2 NONVOLATILE REGISTER MEMORY

This memory can be grouped into two uses of nonvolatile memory. These are the DAC Output Value and Configuration registers:

- Nonvolatile DAC0 and DAC1 Output Value Registers
- · Nonvolatile VREF Select Register
- · Nonvolatile Power-Down Configuration Register
- · Nonvolatile Gain Register

The nonvolatile memory starts functioning below the device's V<sub>POR</sub>/V<sub>BOR</sub> trip point, and is loaded into the corresponding volatile registers whenever the device rises above the POR/BOR voltage trip point.

The device starts writing the EEPROM memory location at the completion of the serial interface command. For the SPI interface, this is when the  $\overline{\text{CS}}$  pin goes inactive (V<sub>IH</sub>).

**Note:** When the nonvolatile memory is written, the corresponding volatile memory is **not** modified.

The nonvolatile DAC registers enable stand-alone operation of the device (without Microcontroller control) after being programmed to the desired value.

Address	Function	Config Bit <sup>(1)</sup>
10h	Nonvolatile DAC0 Register	DL0
11h	Nonvolatile DAC1 Register	DL1
12h	Reserved	_
13h	Reserved	_
14h	Reserved	_
15h	Reserved	_
16h	Reserved	_
17h	Reserved	_
18h	Nonvolatile V <sub>REF</sub> Register	_
19h	Nonvolatile Power-Down Register	_
1Ah	NV Gain Register	_
1Bh	Reserved	_
1Ch	Reserved	_
1Dh	Reserved	
1Eh	Reserved	_
1Fh	Reserved	_

Nonvolatile Memory address range

Note 1: Device Configuration Memory bits require a High-Voltage enable or disable command ( $\overline{LAT}/\overline{LAT0} = V_{IHH}$ , or  $\overline{CS} = V_{IHH}$ ) to modify the bit value.

## 4.2.3 DEVICE CONFIGURATION MEMORY

There are up to five nonvolatile user bits that are not directly mapped into the address space. These nonvolatile device configuration bits control the following functions:

- · DAC Register
- Configuration WiperLock Technology (2 bits per DAC)

The Status register shows the states of the device WiperLock Technology configuration bits. The Status register is described in Register 4-6.

The operation of WiperLock Technology is discussed in **Section 4.2.6** "WiperLock Technology".

#### 4.2.4 UNIMPLEMENTED REGISTER BITS

Read commands of a valid location will read unimplemented bits as '0'.

## 4.2.5 UNIMPLEMENTED (RESERVED) LOCATIONS

Normal (voltage) commands (read or write) to any unimplemented memory address (reserved) will result in a command error condition (CMDERR). Read commands of a reserved location will read bits as '1'.

High-Voltage commands (enable or disable) to any unimplemented configuration bits will result in a command error condition (CMDERR).

## 4.2.5.1 Default Factory POR Memory State of Nonvolatile Memory (EEPROM)

Table 4-2 shows the default factory POR initialization of the device memory map for the 8-, 10- and 12-bit devices.

**Note:** The volatile memory locations will be determined by the nonvolatile memory states (registers and device configuration bits).

TABLE 4-2: FACTORY DEFAULT POR / BOR VALUES

SS		POF	POR/BOR Value					
Address	Function	8-bit	10-bit	12-bit				
00h	Volatile DAC0 Register	7Fh	1FFh	7FFh				
01h	Volatile DAC1 Register	7Fh	1FFh	7FFh				
02h	Reserved (1)	FFh	3FFh	FFFh				
03h	Reserved (1)	FFh	3FFh	FFFh				
04h	Reserved (1)	FFh	3FFh	FFFh				
05h	Reserved (1)	FFh	3FFh	FFFh				
06h	Reserved (1)	FFh	3FFh	FFFh				
07h	Reserved (1)	FFh	3FFh	FFFh				
08h	V <sub>REF</sub> Register	0000h	0000h	0000h				
09h	Power-Down Register	0000h	0000h	0000h				
0Ah	Gain and Status Register	0080h	0080h	0080h				
0Bh	WiperLock™ Technology Status Register	0000h	0000h	0000h				
0Ch	Reserved (1)	FFh	3FFh	FFFh				
0Dh	Reserved (1)	FFh	3FFh	FFFh				
0Eh	Reserved (1)	FFh	3FFh	FFFh				
0Fh	Reserved (1)	FFh	3FFh	FFFh				

SS		POR/BOR Value				
Address	Function	8-bit	10-bit	12-bit		
10h	Nonvolatile DAC0 Register	7Fh	1FFh	7FFh		
11h	Nonvolatile DAC1 Register	7Fh	1FFh	7FFh		
12h	Reserved (1)	FFh	3FFh	FFFh		
13h	Reserved (1)	FFh	3FFh	FFFh		
14h	Reserved (1)	FFh	3FFh	FFFh		
15h	Reserved (1)	FFh	3FFh	FFFh		
16h	Reserved (1)	FFh	3FFh	FFFh		
17h	Reserved (1)	FFh	3FFh	FFFh		
18h	Nonvolatile V <sub>REF</sub> Register	0000h	0000h	0000h		
19h	Nonvolatile Power-Down Register	0000h	0000h	0000h		
1Ah	NV Gain	0000h	0000h	0000h		
1Bh	Reserved <sup>(1)</sup>	FFh	3FFh	FFFh		
1Ch	Reserved (1)	FFh	3FFh	FFFh		
1Dh	Reserved (1)	FFh	3FFh	FFFh		
1Eh	Reserved (1)	FFh	3FFh	FFFh		
1Fh	Reserved (1)	FFh	3FFh	FFFh		

Volatile Memory address range

Nonvolatile Memory address range

Note 1: Reading a reserved memory location will result in the SPI command Command Error condition. The SDO pin will output all '0's. Forcing the CS pin to the V<sub>IH</sub> state will reset the SPI interface.

#### 4.2.6 WIPERLOCK TECHNOLOGY

The MCP48FEBXX device's WiperLock technology allows application-specific device settings (DAC register and configuration) to be secured without requiring the use of an additional write-protect pin. There are two configuration bits (DLx:CLx) for each DAC (DAC0 and DAC1).

Dependent on the state of the DLx:CLx configuration bits, WiperLock technology prevents the serial commands from the following actions on the DACx registers and bits:

- Writing to the specified volatile DACx Register memory location
- Writing to the specified nonvolatile DACx Register memory location
- Writing to the specified volatile DACx configuration bits
- Writing to the specified nonvolatile DACx configuration bits

Each pair of these configuration bits control one of four modes. These modes are shown in Table 4-3. The addresses for the configuration bits are shown in Table 4-1.

To modify the configuration bits, the HVC pin must be forced to the  $V_{IHH}$  state and then receive an enable or disable command on the desired pair of DAC Register addresses.

**Note:** To modify the CL0 bit, the enable or disable command specifies address 00h, while to modify the DL0 bit, the enable or disable command specifies address 10h.

Please refer to Section 7.4 "Enable Configuration Bit" and Section 7.5 "Disable Configuration Bit" commands for operation.

Note:	During device communication, if the
	Device Address/Command combination is
	invalid or an unimplemented Address is
	specified, then the MCP48FEBXX will
	Command Error that Command byte. To
	reset the serial interface state machine,
	the $\overline{\text{CS}}$ pin must be driven to the inactive
	state (V <sub>IH</sub> ) before returning to the active
	state (V <sub>IL</sub> or V <sub>IHH</sub> ).

## 4.2.6.1 POR/BOR Operation with WiperLock Technology Enabled

The WiperLock Technology state is not affected by a POR/BOR event. A POR/BOR event will load the Volatile DAC0 (DAC1) register values with the Nonvolatile DAC0 (DAC1) register values.

TABLE 4-3: WIPERLOCK™ TECHNOLOGY CONFIGURATION BITS - FUNCTIONAL DESCRIPTION

<del>(</del> )		Registe	er / Bits					
DLx:CLx	D	ACx	DACx Con	figuration <sup>(2)</sup>	Comments			
DLx	Volatile Nonvolatile		atile Nonvolatile Volatile Nonvolatile					
11	Locked	Locked	Locked	Locked	All DACx registers are locked.			
10	Locked	Locked	Unlocked	Locked	All DACx registers are locked except volatile DACx Configuration registers. This allows operation of power-down modes.			
01	Unlocked	Locked	Unlocked	Locked	Volatile DACx registers unlocked, nonvolatile DACx registers locked.			
00	Unlocked	Unlocked	Unlocked	Unlocked	All DACx registers are unlocked.			

Note 1: The state of these configuration bits (DLx:CLx) are reflected in WLxB:WLxA bits as shown in Register 4-6.

**<sup>2:</sup>** DAC configuration bits include Voltage Reference Control bits (VRxB:VRxA), Power-Down Control bits (PDxB:PDxA), and Output Gain bits (Gx).

#### 4.2.7 DEVICE REGISTERS

12-bit

10-bit

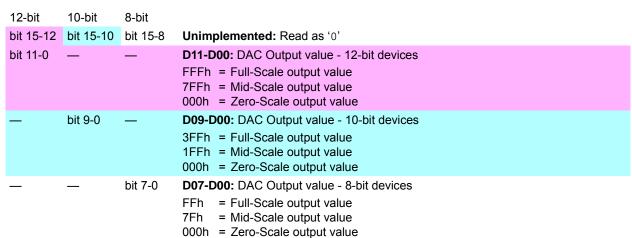
8-bit

Register 4-1 shows the format of the DAC Output Value registers for both the volatile memory locations and the nonvolatile memory locations. These registers will be either 8 bits, 10 bits, or 12 bits wide. The values are right justified.

#### REGISTER 4-1: DAC0 AND DAC1 REGISTERS (VOLATILE AND NONVOLATILE)

U-0 U-0 U-0 U-0 R/W-0 D11 D10 D09 D08 D07 D06 D05 D04 D03 D02 D01 D00 \_\_(1) \_\_(1) D09 D08 D07 D06 D05 D04 D03 D02 D01 D00 \_\_(1) \_\_(1) \_\_(1) \_\_(1) D07 D06 D05 D04 D03 D02 D01 D00 bit 15 bit 0

Legend:			
R = Readable bit -n = Value at POR = 12-bit device	W = Writable bit '1' = Bit is set = 10-bit device	U = Unimplemented bit, read as '0' '0' = Bit is cleared = 8-bit device	x = Bit is unknown



Note 1: Unimplemented bit, read as '0'.

Register 4-2 shows the format of the Voltage Reference Control Register. Each DAC has two bits to control the source of the voltage reference of the DAC. This register is for both the volatile memory locations and the nonvolatile memory locations.

## REGISTER 4-2: VOLTAGE REFERENCE (VREF) CONTROL REGISTER (VOLATILE AND NONVOLATILE) (ADDRESSES 08h AND 18h)

Single Dual

	U-0	U-0	U-0	U-0	U-0	U-0	U-0	U-0	U-0	U-0	U-0	U-0	R/W-0	R/W-0	R/W-0	R/W-0
:		_	_	_	_	_	_	_	_	_	_	_	(1)	(1)	VR0B	VR0A
		_	_	_	_	_	_	_	_	_	_	_	VR1B	VR1A	VR0B	VR0A
	bit 15															bit 0

Legend:			
R = Readable bit	W = Writable bit	U = Unimplemented bit, read as '0'	
-n = Value at POR	'1' = Bit is set	'0' = Bit is cleared	x = Bit is unknown
= Single-channel d	evice	= Dual-channel device	

Dual	
bit 15-4	Unimplemented: Read as '0'
bit 3-0	VRxB-VRxA: DAC Voltage Reference Control bits
	11 = V <sub>REF</sub> pin (Buffered); V <sub>REF</sub> buffer enabled
	10 = V <sub>REF</sub> pin (Unbuffered); V <sub>REF</sub> buffer disabled
	01 = Internal Band Gap (1.22V typical); V <sub>REF</sub> buffer enabled
	V <sub>REF</sub> voltage driven when powered-down
	00 = V <sub>DD</sub> (Unbuffered); V <sub>REF</sub> buffer disabled.
	Use this state with Power-Down bits for lowest current.
	bit 15-4

Note 1: Unimplemented bit, read as '0'.

Register 4-3 shows the format of the Power-Down Control Register. Each DAC has two bits to control the Power-Down state of the DAC. This register is for both the volatile memory locations and the nonvolatile memory locations.

## REGISTER 4-3: POWER-DOWN CONTROL REGISTER (VOLATILE AND NONVOLATILE) (ADDRESSES 09h, 19h)

Single Dual

U-0	U-0	U-0	U-0	U-0	U-0	U-0	U-0	U-0	U-0	U-0	U-0	R/W-0	R/W-0	R/W-0	R/W-0
_	_	_	_	_	_	_	_	_	_	_	_	(1)	(1)	PD0B	PD0A
_	_	_	_	_	_	_	_	_	_	_	_	PD1B	PD1A	PD0B	PD0A
bit 15															bit 0

Legend:			
R = Readable bit	W = Writable bit	U = Unimplemented bit, read as '0'	
-n = Value at POR	'1' = Bit is set	'0' = Bit is cleared	x = Bit is unknown
= Single-channel d	evice	= Dual-channel device	

Single	Dual	
bit 15-2	bit 15-4	Unimplemented: Read as '0'
bit 1-0	bit 3-0	PDxB-PDxA: DAC Power-Down Control bits <sup>(2)</sup>
		11 = Powered Down - V <sub>OUT</sub> is open circuit.
		10 = Powered Down - $V_{OUT}$ is loaded with a 100 kΩ resistor to ground.
		01 = Powered Down - $V_{OUT}$ is loaded with a 1 kΩ resistor to ground.
		00 = Normal Operation (Not powered-down)

Note 1: Unimplemented bit, read as '0'.

2: See Table 5-5 and Figure 5-10 for more details.

Register 4-4 shows the format of the volatile Gain Control and System Status Register. Each DAC has one bit to control the gain of the DAC and three Status bits.

### REGISTER 4-4: GAIN CONTROL AND SYSTEM STATUS REGISTER (VOLATILE) (ADDRESS 0Ah)

Single Dual

	U-0	U-0	U-0	U-0	U-0	U-0	R/W-0	R/W-0	R/C-1	R-0	U-0	U-0	U-0	U-0	U-0	U-0
	_	_	_	_	_	_	(1)	G0	POR	EEWA	_	_	_	_	_	_
	_	_	_	_			G1	G0	POR	EEWA	_	l				_
ſ	bit 15	•		•	•	•		•							•	bit 0

Legend:			
R = Readable bit -n = Value at POR = Single-channel de	W = Writable bit '1' = Bit is set evice	C = Clear-able bit '0' = Bit is cleared = Dual-channel device	U = Unimplemented bit, read as '0' x = Bit is unknown

Single	Dual	
bit 15-	9 bit 15-10	Unimplemented: Read as '0'
_	bit 9	G1: DAC1 Output Driver Gain control bits (Dual-Channel Device only)  1 = 2x Gain  0 = 1x Gain
bit 8	bit 8	G0: DAC0 Output Driver Gain control bits  1 = 2x Gain  0 = 1x Gain
bit 7	bit 7	POR: Power-on Reset (Brown-out Reset) Status bit This bit indicates if a Power-on Reset (POR) or Brown-out Reset (BOR) event has occurred since the last read command of this register. Reading this register clears the state of the POR Status bit.
		<ul> <li>1 = A POR (BOR) event occurred since the last read of this register. Reading this register clears this bit.</li> <li>0 = A POR (BOR) event has not occurred since the last read of this register.</li> </ul>
bit 6	bit 6	<b>EEWA:</b> EEPROM Write Active Status bit This bit indicates if the EEPROM Write Cycle is occurring.
		<ul> <li>1 = An EEPROM Write Cycle is currently occurring. Only serial commands to the volatile memory are allowed.</li> <li>0 = An EEPROM Write Cycle is NOT currently occurring.</li> </ul>
bit 5-0	bit 5-0	Unimplemented: Read as '0'

Note 1: Unimplemented bit, read as '0'.

Register 4-5 shows the format of the Nonvolatile Gain Control Register. Each DAC has one bit to control the gain of the DAC.

### REGISTER 4-5: GAIN CONTROL REGISTER (NONVOLATILE) (ADDRESS 1Ah)

Single Dual

U-0	U-0	U-0	U-0	U-0	R/W-0	R/W-0	U-0								
_	_	_	_	_	_	(1)	G0	_	_	_	_	_	_	_	_
_	_	_	_	_	_	G1	G0	_	_	_	_	_	_	_	_
bit 15								•	•						bit 0

Legend:						
R = Readable bit	W = Writable bit	U = Unimplemented bit, read as '0'				
-n = Value at POR	'1' = Bit is set	'0' = Bit is cleared	x = Bit is unknown			
= Single-channel d	evice	= Dual-channel device				

Single	Dual	
bit 15-9	bit 15-10	Unimplemented: Read as '0'
_	bit 9	G1: DAC1 Output Driver Gain control bits (Dual-Channel Device only)  1 = 2x Gain  0 = 1x Gain
bit 8	bit 8	G0: DAC0 Output Driver Gain control bits  1 = 2x Gain  0 = 1x Gain
bit 7-0	bit 6-0	Unimplemented: Read as '0'

Note 1: Unimplemented bit, read as '0'.

Register 4-6 shows the format of the DAC WiperLock Technology Status Register.

### REGISTER 4-6: DAC WIPERLOCK TECHNOLOGY STATUS REGISTER (VOLATILE) (ADDRESS 0BH)

Single Dual

	U-0	U-0	U-0	U-0	U-0	U-0	U-0	U-0	U-0	U-0	U-0	U-0	R-0 <sup>(1)</sup>	R-0 <sup>(1)</sup>	R-0 <sup>(1)</sup>	R-0 <sup>(1)</sup>
Э	1	_	_	_	_	_	1	I	_	_	_	_	( <del>2</del> )	( <u>2</u> )	WL0B	WL0A
	_	_	_	_	_	_	_	_	_	_	_	_	WL1B	WL1A	WL0B	WL0A
	bit 15															bit 0

Legend:						
R = Readable bit	W = Writable bit	U = Unimplemented bit, read as '0'				
-n = Value at POR	'1' = Bit is set	'0' = Bit is cleared	x = Bit is unknown			
= Single-channel de	vice	= Dual-channel device				

Single	Dual	
bit 15-2	bit 15-4	Unimplemented: Read as '0'
bit 1-0	bit 3-0	<b>WLxB-WLxA:</b> WiperLock Technology Status bits: These bits reflect the state of the DLx:CLx nonvolatile configuration bits.
		<ul><li>11 = DAC wiper and DAC Configuration (volatile and nonvolatile registers) are locked.</li><li>(DLx = CLx = Enabled)</li></ul>
		10 = DAC wiper (volatile and nonvolatile) and DAC Configuration (nonvolatile registers) are locked (DLx = Enabled; CLx = Disabled).
		<ul><li>01 = DAC wiper (nonvolatile) and DAC Configuration (nonvolatile registers) are locked.</li><li>(DLx = Disabled; CLx = Enabled)</li></ul>
		00 = DAC wiper and DAC Configuration are unlocked (DLx = CLx = Disabled).

- **Note 1:** POR Value dependent on the programmed values of the DLx:CLx configuration bits. The devices are shipped with a default DLx:CLx configuration bit state of '0'.
  - 2: Unimplemented bit, read as '0'.

**NOTES:** 

### 5.0 DAC CIRCUITRY

The Digital-to-Analog Converter circuitry converts a digital value into its analog representation. The description details the functional operation of the device.

The DAC Circuit uses a resistor ladder implementation. Devices have up to two DACs.

Figure 5-1 shows the functional block diagram for the MCP48FEBXX DAC circuitry.

The functional blocks of the DAC include:

- Resistor Ladder
- Voltage Reference Selection
- Output Buffer/V<sub>OUT</sub> Operation
- Internal Band Gap (as a voltage reference)
- Latch Pin (LAT)
- Power-Down Operation

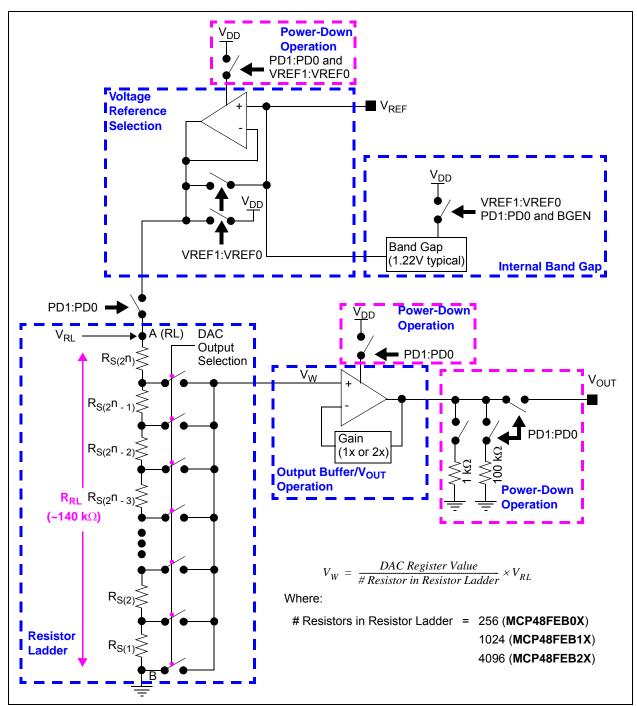


FIGURE 5-1: MCP48FEBXX DAC Module Block Diagram.

#### 5.1 **Resistor Ladder**

The Resistor Ladder is a digital potentiometer with the B terminal internally grounded and the A terminal connected to the selected reference voltage (see Figure 5-2). The volatile DAC register controls the wiper position. The wiper voltage (V<sub>W</sub>) is proportional to the DAC register value divided by the number of resistor elements (R<sub>S</sub>) in the ladder (256, 1024 or 4096) related to the V<sub>RI</sub> voltage.

The output of the resistor network will drive the input of an output buffer.

The Resistor Network is made up of these three parts:

- · Resistor Ladder (string of R<sub>S</sub> elements)
- · Wiper switches
- · DAC Register decode

The resistor ladder (R<sub>RL</sub>) has a typical impedance of approximately 140 k $\Omega$ . This resistor ladder resistance (R<sub>RI</sub>) may vary from device to device by up to ±20%. Since this is a voltage divider configuration, the actual R<sub>RI</sub> resistance does not affect the output given a fixed voltage at V<sub>RI</sub>.

Equation 5-1 shows the calculation for the step resistance:

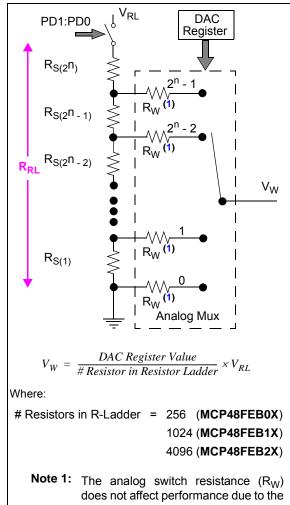
#### **EQUATION 5-1:** R<sub>S</sub> CALCULATION

$$R_{S} = \frac{R_{RL}}{(256)}$$
 8-bit Device  $R_{S} = \frac{R_{RL}}{(1024)}$  10-bit Device  $R_{S} = \frac{R_{RL}}{(4096)}$  12-bit Device

Note: The maximum wiper position is  $2^n - 1$ , while the number of resistors in the resistor ladder is 2<sup>n</sup>. This means that when the DAC register is at full-scale, there is one resistor element  $(R_S)$ between the wiper and the  $V_{\text{RL}}$  voltage.

If the unbuffered  $V_{REF}$  pin is used as the  $V_{RL}$  voltage source, this voltage source should have a low output impedance.

When the DAC is powered-down, the resistor ladder is disconnected from the selected reference voltage.



voltage divider configuration.

FIGURE 5-2: Resistor Ladder Model Block Diagram.

### 5.2 Voltage Reference Selection

The resistor ladder has up to four sources for the reference voltage. Two user control bits (VREF1:VREF0) are used to control the selection, with the selection connected to the  $V_{RL}$  node (see Figures 5-3 and 5-4). The four voltage source options for the Resistor Ladder are:

- 1. V<sub>DD</sub> pin voltage
- 2. Internal Voltage Reference (V<sub>BG</sub>)
- 3. V<sub>REF</sub> pin voltage unbuffered
- 4. V<sub>REF</sub> pin voltage internally buffered

The selection of the voltage is specified with the volatile  $V_{REF1}$ : $V_{REF0}$  configuration bits (see Register 4-2). There are nonvolatile and volatile VREF1:VREF0 configuration bits. On a POR/BOR event, the state of the nonvolatile VREF1:VREF0 configuration bits is latched into the volatile VREF1:VREF0 configuration bits.

When the user selects the  $V_{DD}$  as reference, the  $V_{REF}$  pin voltage is not connected to the resistor ladder.

If the  $V_{\mbox{\scriptsize REF}}$  pin is selected, then a selection has to be made between the Buffered or Unbuffered mode.

### 5.2.1 UNBUFFERED MODE

The  $V_{REF}$  pin voltage may be from  $V_{SS}$  to  $V_{DD}$ .

- Note 1: The voltage source should have a low output impedance. If the voltage source has a high output impedance, then the voltage on the  $V_{REF}$ 's pin would be lower than expected. The resistor ladder has a typical impedance of 140 k $\Omega$  and a typical capacitance of 29 pF.
  - 2: If the V<sub>REF</sub> pin is tied to the V<sub>DD</sub> voltage, V<sub>DD</sub> mode (VREF1:VREF0 = '00') is recommended.

### 5.2.2 BUFFERED MODE

The  $V_{REF}$  pin voltage may be from 0.01V to  $V_{DD}$ -0.04V. The input buffer (amplifier) provides low offset voltage, low noise, and a very high input impedance, with only minor limitations on the input range and frequency response.

- Note 1: Any variation or noises on the reference source can directly affect the DAC output. The reference voltage needs to be as clean as possible for accurate DAC performance.
  - 2: If the  $V_{REF}$  pin is tied to the  $V_{DD}$  voltage,  $V_{DD}$  mode (VREF1:VREF0 = '00') is recommended.

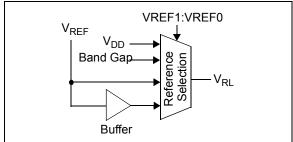
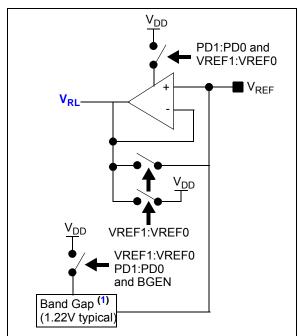


FIGURE 5-3: Resistor Ladder Reference Voltage Selection Block Diagram.



Note 1: The Band Gap voltage (V<sub>BG</sub>) is 1.22V typical. The band gap output goes through the buffer with a 2x gain to create the V<sub>RL</sub> voltage. See Section 5.4 "Internal Band Gap" for additional information on the band gap circuit.

FIGURE 5-4: Reference Voltage Selection Implementation Block Diagram.

### 5.2.3 BAND GAP MODE

If the Internal Band Gap is selected, then the external  $V_{REF}$  pin should not be driven and only use high-impedance loads. Decoupling capacitors are recommended for optimal operation.

The band gap output is buffered, but the internal switches limit the current that the output should source to the  $V_{REF}$  pin. The resistor ladder buffer is used to drive the Band Gap voltage for the cases of multiple DAC outputs. This ensures that the resistor ladders are always properly sourced when the band gap is selected.

### 5.3 Output Buffer/V<sub>OUT</sub> Operation

The Output Driver buffers the wiper voltage  $(V_W)$  of the Resistor Ladder.

The DAC output is buffered with a low power and precision output amplifier (op amp). This amplifier provides a rail-to-rail output with low offset voltage and low noise. The amplifier's output can drive the resistive and high-capacitive loads without oscillation. The amplifier provides a maximum load current which is enough for most programmable voltage reference applications. Refer to Section 1.0 "Electrical Characteristics" for the specifications of the output amplifier.

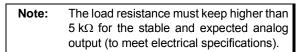


Figure 5-5 shows the block diagram of the output driver circuit.

The user can select the output gain of the output amplifier. The gain options are:

- a) Gain of 1, with either the  $V_{DD}$  or  $V_{REF}$  pin used as reference voltage.
- b) Gain of 2.

Power-down logic also controls the output buffer operation (see Section 5.6 "Power-Down Operation" for additional information on Power-Down). In any of the three power-down modes, the op amp is powered-down and its output becomes a high impedance to the  $V_{OUT}$  pin.

Table 5-1 shows the gain bit operation.

TABLE 5-1: OUTPUT DRIVER GAIN

Gain Bit	Gain	Comment					
0	1						
1	2	Limits V <sub>REF</sub> pin voltages relative to device V <sub>DD</sub> voltage.					

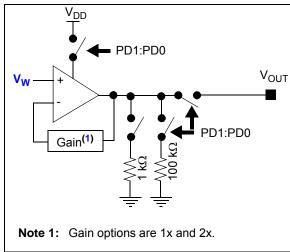


FIGURE 5-5:

Output Driver Block Diagram.

### 5.3.1 PROGRAMMABLE GAIN

The amplifier's gain is controlled by the Gain (G) configuration bit (see Register 4-5) and the  $V_{RL}$  reference selection.

The volatile G bit value can be modified by:

- POR events
- BOR events
- · SPI write commands

### 5.3.2 OUTPUT VOLTAGE

The volatile DAC Register values, along with the device's configuration bits, control the analog  $V_{OUT}$  voltage. The volatile DAC Register's value is unsigned binary. The formula for the output voltage is given in Equation 5-2. Table 5-3 shows examples of volatile DAC register values and the corresponding theoretical  $V_{OUT}$  voltage for the MCP48FEBXX devices.

# EQUATION 5-2: CALCULATING OUTPUT VOLTAGE (V<sub>OUT</sub>)

$$V_{OUT} = rac{V_{RL} imes DAC\ Register\ Value}{\#\ Resistor\ in\ Resistor\ Ladder} imes Gain$$

Where:

# Resistors in R-Ladder = 4096 (MCP48FEB2X) 1024 (MCP48FEB1X) 256 (MCP48FEB0X)

Note: When Gain = 2 ( $V_{RL} = V_{REF}$ ) and if  $V_{REF} > V_{DD}$  / 2, the  $V_{OUT}$  voltage will be limited to  $V_{DD}$ . So if  $V_{REF} = V_{DD}$ , then the  $V_{OUT}$  voltage will not change for volatile DAC Register values mid-scale and greater, since the op amp is at full-scale output.

The following events update the DAC register value and therefore the analog voltage output ( $V_{OUT}$ ):

- · Power-on Reset
- · Brown-out Reset
- Write command

The  $V_{OUT}$  voltage will start driving to the new value after the event has occurred.

### 5.3.3 STEP VOLTAGE (V<sub>S</sub>)

The Step Voltage is dependent on the device resolution and the calculated output voltage range. One LSb is defined as the ideal voltage difference between two successive codes. The step voltage can easily be calculated by using Equation 5-3 (DAC Register Value is equal to 1). Theoretical step voltages are shown in Table 5-2 for several  $V_{\rm REF}$  voltages.

### **EQUATION 5-3:** V<sub>S</sub> CALCULATION

$$V_S = \frac{V_{RL}}{\# Resistor\ in\ Resistor\ Ladder} \times Gain$$
 Where: 
$$\# \ Resistors\ in\ R-Ladder \ = \ 4096\ (\textbf{12-bit})$$
 
$$1024\ (\textbf{10-bit})$$
 
$$256\ (\textbf{8-bit})$$

# TABLE 5-2: THEORETICAL STEP VOLTAGE (V<sub>S</sub>) (1)

		V <sub>REF</sub>										
	5.0	2.7	1.8	1.5	1.0							
	1.22 mV	659 uV	439 uV	366 uV	244 uV	12-bit						
$v_s$	4.88 mV	2.64 mV	1.76 mV	1.46 mV	977 uV	10-bit						
	19.5 mV	10.5 mV	7.03 mV	5.86 mV	3.91 mV	8-bit						

**Note 1:** When Gain = 1x,  $V_{FS} = V_{RL}$ , and  $V_{ZS} = 0V$ .

### 5.3.4 OUTPUT SLEW RATE

Figure 5-6 shows an example of the slew rate of the  $V_{OUT}$  pin. The slew rate can be affected by the characteristics of the circuit connected to the  $V_{OUT}$  pin.

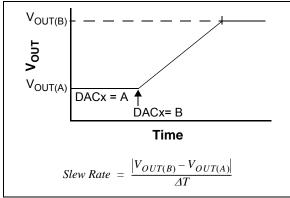


FIGURE 5-6:

V<sub>OUT</sub> pin Slew Rate.

### 5.3.4.1 Small Capacitive Load

With a small capacitive load, the output buffer's current is not affected by the capacitive load ( $C_L$ ). But still, the  $V_{OUT}$  pin's voltage is not a step transition from one output value (DAC register value) to the next output value. The change of the  $V_{OUT}$  voltage is limited by the output buffer's characteristics, so the  $V_{OUT}$  pin voltage will have a slope from the old voltage to the new voltage. This slope is fixed for the output buffer, and is referred to as the buffer slew rate ( $SR_{BUF}$ ).

### 5.3.4.2 Large Capacitive Load

With a larger capacitive load, the slew rate is determined by two factors:

- The output buffer's short-circuit current (I<sub>SC</sub>)
- The V<sub>OUT</sub> pin's external load

 $I_{OUT}$  cannot exceed the output buffer's short-circuit current ( $I_{SC}$ ), which fixes the output buffer slew rate ( $SR_{BUF}$ ). The voltage on the capacitive load ( $C_L$ ),  $V_{CL}$ , changes at a rate proportional to  $I_{OUT}$ , which fixes a capacitive load slew rate ( $SR_{CL}$ ).

The  $V_{CL}$  voltage slew rate is limited to the slower of the output buffer's internally set slew rate (SRBUF) and the capacitive load slew rate (SR $_{CL}$ ).

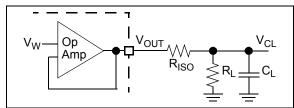
## 5.3.5 DRIVING RESISTIVE AND CAPACITIVE LOADS

The  $V_{OUT}$  pin can drive up to 100 pF of capacitive load in parallel with a 5 k $\Omega$  resistive load (to meet electrical specifications). A  $V_{OUT}$  vs. Resistive Load characterization graph is provided in the Typical Performance Curves for this device (**DS20005440**).

 $V_{OUT}$  drops slowly as the load resistance decreases after about 3.5 k $\Omega.$  It is recommended to use a load with  $R_L$  greater than 5 k $\Omega.$ 

Driving large capacitive loads can cause stability problems for voltage feedback op amps. As the load capacitance increases, the feedback loop's phase margin decreases and the closed-loop bandwidth is reduced. This produces gain peaking in the frequency response with overshoot and ringing in the step response. That is, since the  $V_{\rm OUT}$  pin's voltage does not quickly follow the buffer's input voltage (due to the large capacitive load), the output buffer will overshoot the desired target voltage. Once the driver detects this overshoot, it compensates by forcing it to a voltage below the target. This causes voltage ringing on the  $V_{\rm OUT}$  pin.

When driving large capacitive loads with the output buffer, a small series resistor ( $R_{\rm ISO}$ ) at the output (see Figure 5-7) improves the output buffer's stability (feedback loop's phase margin) by making the output load resistive at higher frequencies. The bandwidth will be generally lower than the bandwidth with no capacitive load.



**FIGURE 5-7:** Circuit to Stabilize Output Buffer for Large Capacitive Loads (C<sub>L</sub>).

The  $R_{ISO}$  resistor value for your circuit needs to be selected. The resulting frequency response peaking and step response overshoot for this  $R_{ISO}$  resistor value should be verified on the bench. Modify the  $R_{ISO}$ 's resistance value until the output characteristics meet your requirements.

A method to evaluate the system's performance is to inject a step voltage on the  $V_{REF}$  pin and observe the  $V_{OUT}$  pin's characteristics.

Note: Additional insight into circuit design for driving capacitive loads can be found in AN884 – "Driving Capacitive Loads With Op Amps" (DS00884).

TABLE 5-3: DAC INPUT CODE VS. CALCULATED ANALOG OUTPUT (V<sub>OUT</sub>) (V<sub>DD</sub> = 5.0V)

Davida	Volatile DAC	v (1)	LSI	)	Gain	V <sub>OUT</sub> (3)	
Device	Register Value	<b>V</b> <sub>RL</sub> <sup>(1)</sup>	Equation	μV	Selection (2)	Equation	V
	1111 1111 1111	5.0V	5.0V/4096	1,220.7	1x	V <sub>RL</sub> * (4095/4096) * 1	4.998779
		2.5V	2.5V/4096	610.4	1x	V <sub>RL</sub> * (4095/4096) * 1	2.499390
					2x <sup>(2)</sup>	V <sub>RL</sub> * (4095/4096) * 2)	4.998779
MCP48FEB2X (12-bit)	0111 1111 1111	5.0V	5.0V/4096	1,220.7	1x	V <sub>RL</sub> * (2047/4096) * 1)	2.498779
(12		2.5V	2.5V/4096	610.4	1x	V <sub>RL</sub> * (2047/4096) * 1)	1.249390
32X					2x <sup>(2)</sup>	V <sub>RL</sub> * (2047/4096) * 2)	2.498779
	0011 1111 1111	5.0V	5.0V/4096	1,220.7	1x	V <sub>RL</sub> * (1023/4096) * 1)	1.248779
948		2.5V	2.5V/4096	610.4	1x	V <sub>RL</sub> * (1023/4096) * 1)	0.624390
Ğ					2x <sup>(2)</sup>	V <sub>RL</sub> * (1023/4096) * 2)	1.248779
_	0000 0000 0000	5.0V	5.0V/4096	1,220.7	1x	V <sub>RL</sub> * (0/4096) * 1)	0
		2.5V	2.5V/4096	610.4	1x	V <sub>RL</sub> * (0/4096) * 1)	0
					2x <sup>(2)</sup>	V <sub>RL</sub> * (0/4096) * 2)	0
	11 1111 1111	5.0V	5.0V/1024	4,882.8	1x	V <sub>RL</sub> * (1023/1024) * 1	4.995117
		2.5V	2.5V/1024	2,441.4	1x	V <sub>RL</sub> * (1023/1024) * 1	2.497559
					2x <sup>(2)</sup>	V <sub>RL</sub> * (1023/1024) * 2	4.995117
-pit	01 1111 1111	5.0V	5.0V/1024	4,882.8	1x	V <sub>RL</sub> * (511/1024) * 1	2.495117
(10		2.5V	2.5V/1024	2,441.4	1x	V <sub>RL</sub> * (511/1024) * 1	1.247559
31X					2x <sup>(2)</sup>	V <sub>RL</sub> * (511/1024) * 2	2.495117
MCP48FEB1X (10-bit)	00 1111 1111	5.0V	5.0V/1024	4,882.8	1x	V <sub>RL</sub> * (255/1024) * 1	1.245117
948		2.5V	2.5V/1024	2,441.4	1x	V <sub>RL</sub> * (255/1024) * 1	0.622559
Š K					2x <sup>(2)</sup>	V <sub>RL</sub> * (255/1024) * 2	1.245117
	00 0000 0000	5.0V	5.0V/1024	4,882.8	1x	V <sub>RL</sub> * (0/1024) * 1	0
		2.5V	2.5V/1024	2,441.4	1x	V <sub>RL</sub> * (0/1024) * 1	0
					2x <sup>(2)</sup>	V <sub>RL</sub> * (0/1024) * 1	0
	1111 1111	5.0V	5.0V/256	19,531.3	1x	V <sub>RL</sub> * (255/256) * 1	4.980469
		2.5V	2.5V/256	9,765.6	1x	V <sub>RL</sub> * (255/256) * 1	2.490234
					2x <sup>(2)</sup>	V <sub>RL</sub> * (255/256) * 2	4.980469
(8-bit)	0111 1111	5.0V	5.0V/256	19,531.3	1x	V <sub>RL</sub> * (127/256) * 1	2.480469
(8)		2.5V	2.5V/256	9,765.6	1x	V <sub>RL</sub> * (127/256) * 1	1.240234
B0)					2x <sup>(2)</sup>	V <sub>RL</sub> * (127/256) * 2	2.480469
MCP48FEB0	0011 1111	5.0V	5.0V/256	19,531.3	1x	V <sub>RL</sub> * (63/256) * 1	1.230469
P48		2.5V	2.5V/256	9,765.6	1x	V <sub>RL</sub> * (63/256) * 1	0.615234
<b>⊠</b>					2x <sup>(2)</sup>	V <sub>RL</sub> * (63/256) * 2	1.230469
	0000 0000	5.0V	5.0V/256	19,531.3	1x	V <sub>RL</sub> * (0/256) * 1	0
		2.5V	2.5V/256	9,765.6	1x	V <sub>RL</sub> * (0/256) * 1	0
					2x <sup>(2)</sup>	V <sub>RL</sub> * (0/256) * 2	0

 $\textbf{Note 1:} \quad V_{RL} \text{ is the resistor ladder's reference voltage. It is independent of VREF1:} VREF0 \text{ selection.}$ 

**3:** These theoretical calculations do not take into account the Offset, Gain and Nonlinearity errors.

<sup>2:</sup> Gain selection of 2x (Gx = '1') requires voltage reference source to come from V<sub>REF</sub> pin (VREF1:VREF0 = '10' or '11') and requires V<sub>REF</sub> pin voltage (or V<sub>RL</sub>) ≤ V<sub>DD</sub>/2, or from the internal band gap (VREF1:VREF0 = '01').

### 5.4 Internal Band Gap

The internal band gap is designed to drive the Resistor Ladder Buffer.

The resistance of a resistor ladder (R<sub>RL</sub>) is targeted to be 140 k $\Omega$  (±40 k $\Omega$ ), which means a minimum resistance of 100 k $\Omega$ .

The band gap selection can be used across the  $V_{DD}$  voltages while maximizing the  $V_{OUT}$  voltage ranges. For  $V_{DD}$  voltages below the 2 \* Gain \*  $V_{BG}$  voltage, the output for the upper codes will be clipped to the  $V_{DD}$  voltage. Table 5-4 shows the maximum DAC register code given device VDD and Gain bit setting.

TABLE 5-4: V<sub>OUT</sub> USING BAND GAP

0	DAC Gain	Max D	AC Co	de <sup>(1)</sup>	
V <sub>DD</sub>		12-bit	10-bit	8-bit	Comment
<i></i>	1	FFFh	3FFh	FFh	V <sub>OUT(max)</sub> = 2.44V (2)
5.5	2	FFFh	3FFh	FFh	V <sub>OUT(max)</sub> = 4.88V (2)
0.7	1	FFFh	3FFh	FFh	V <sub>OUT(max)</sub> = 2.44V (2)
2.7	2	8DAh	236h	8Dh	~ 0 to 55% range
2.0 <sup>(</sup>	1	D1Dh	347h	D1h	~ 0 to 82% range
3)	2 <sup>(4)</sup>	68Eh	1A3h	68h	~ 0 to 41% range

Note 1: Without the  $V_{OUT}$  pin voltage being clipped.

- **2:** When  $V_{BG} = 1.22V$  typical.
- 3: Band gap performance achieves full performance starting from a  $\rm V_{DD}$  of 2.0V.
- **4:** It is recommended to use Gain = 1 setting instead.

### 5.5 Latch Pin (LAT)

The Latch pin controls when the volatile DAC Register value is transferred to the DAC wiper. This is useful for applications that need to synchronize the wiper(s) updates to an external event, such as zero crossing or updates to the other wipers on the device. The LAT pin is asynchronous to the serial interface operation.

When the LAT pin is high, transfers from the volatile DAC register to the DAC wiper are inhibited. The volatile DAC register value(s) can be continued to be updated.

When the LAT pin is low, the volatile DAC register value is transferred to the DAC wiper.

Note: This allows both the volatile DAC0 and DAC1 Registers to be updated while the LAT pin is high, and to have outputs synchronously updated as the LAT pin is driven low.

Figure 5-8 shows the interaction of the LAT pin and the loading of the DAC wiper x (from the volatile DAC Register x). The transfers are level driven. If the LAT pin is held low, the corresponding DAC wiper is updated as soon as the volatile DAC Register value is updated.

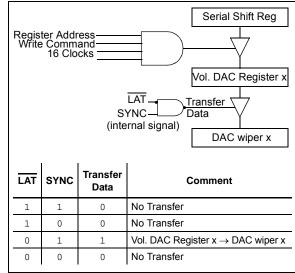


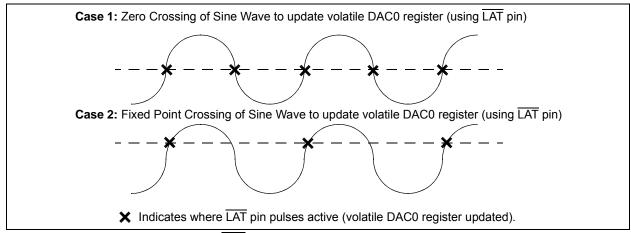
FIGURE 5-8: LAT and DAC Interaction.

The LAT pin allows the DAC wiper to be updated to an external event as well as have multiple DAC channels/devices update at a common event.

Since the DAC wiper x is updated from the Volatile DAC Register x, all DACs that are associated with a given  $\overline{LAT}$  pin can be updated synchronously.

If the application does not require synchronization, then this signal should be tied low.

Figure 5-9 shows two cases of using the LAT pin to control when the wiper register is updated relative to the value of a sine wave signal.



**FIGURE 5-9:** Example use of  $\overline{LAT}$  pin operation.

### 5.6 Power-Down Operation

To allow the application to conserve power when the DAC operation is not required, three power-down modes are available. The Power-Down configuration bits (PD1:PD0) control the power-down operation (Figure 5-10 and Table 5-5). On devices with multiple DACs, each DACs power-down mode is individually controllable. All power-down modes do the following:

- Turn off most the DAC module's internal circuits (output op amp, resistor ladder, et al.)
- Op amp output becomes high-impedance to the  $V_{\mbox{\scriptsize OUT}}$  pin
- Disconnects resistor ladder from reference voltage (V<sub>RL</sub>)
- Retains the value of the volatile DAC register and configuration bits and the nonvolatile (EEPROM) DAC register and configuration bits

Depending on the selected power-down mode, the following will occur:

- V<sub>OUT</sub> pin is switched to one of two resistive pull-downs (See Table 5-5):
  - 100 kΩ (typical)
  - 1 kΩ (typical)
- Op amp is powered-down and the V<sub>OUT</sub> pin becomes high-impedance.

There is a delay ( $T_{PDE}$ ) between the PD1:PD0 bits changing from '00' to either '01', '10' or '11' with the op amp no longer driving the  $V_{OUT}$  output and the pull-down resistors sinking current.

In any of the power-down modes where the  $V_{OUT}$  pin is not externally connected (sinking or sourcing current), the power-down current will typically be ~650 nA for a single-DAC device. As the number of DACs increases, the device's power-down current will also increase.

The Power-Down bits are modified by using a write command to the volatile Power-Down register, or a POR event which transfers the nonvolatile Power-Down register to the volatile Power-Down register.

Section 7.0 "SPI Commands" describes the SPI commands. The Write Command can be used to update the volatile PD1:PD0 bits.

Note: The SPI serial interface circuit is not affected by the Power-Down mode. This circuit remains active in order to receive any command that might come from the host controller device.

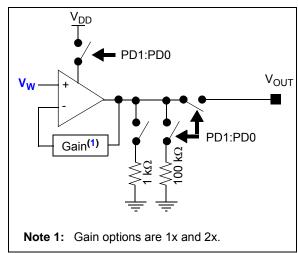


FIGURE 5-10:

V<sub>OUT</sub> Power-Down Block

Diagram.

TABLE 5-5: POWER-DOWN BITS AND OUTPUT RESISTIVE LOAD

PD1	PD0	Function	
0	0	Normal operation	
0	1	1 kΩ resistor to ground	
1	0	100 kΩ resistor to ground	
1	1	Open Circuit	

Table 5-6 shows the current sources for the DAC based on the selected source of the DAC's reference voltage and if the device is in normal operating mode or one of the power-down modes.

TABLE 5-6: DAC CURRENT SOURCES

Device V <sub>DD</sub> Current	PD1:0 = '00', VREF1:0 =				PD1:0 ≠ '00', VREF1:0 =			
Source	00	01	10	11	00	01	10	11
Output Op Amp	Y	Υ	Y	Υ	N	N	N	N
Resistor Ladder	Υ	Y	N <sup>(1)</sup>	Υ	N	N	N <sup>(1)</sup>	N
RL Op Amp	N	Υ	N	Υ	N	N	N	Ν
Band Gap	Ν	Υ	N	Ν	Ν	Υ	N	Ν

Note 1: Current is sourced from the  $V_{REF}$  pin, not the device  $V_{DD}$ .

### 5.6.1 EXITING POWER-DOWN

When the device exits Power-Down mode, the following occurs:

- Disabled circuits (op amp, resistor ladder, et al.) are turned on
- The resistor ladder is connected to selected reference voltage (V<sub>RL</sub>)
- · The selected pull-down resistor is disconnected
- The V<sub>OUT</sub> output will be driven to the voltage represented by the volatile DAC Register's value and configuration bits

The  $V_{OUT}$  output signal will require time as these circuits are powered-up and the output voltage is driven to the specified value as determined by the volatile DAC register and configuration bits.

Note:

Since the op amp and resistor ladder were powered-off (0V), the op amp's input voltage ( $V_W$ ) can be considered 0V. There is a delay ( $T_{PDD}$ ) between the PD1:PD0 bits updating to '00' and the op amp driving the  $V_{OUT}$  output. The op amp's settling time (from 0V) needs to be taken into account to ensure the  $V_{OUT}$  voltage reflects the selected value.

A write command forcing the PD1:PD0 bits to '00', will cause the device to exit the power-down mode.

# 5.7 DAC Registers, Configuration Bits, and Status Bits

The MCP48FEBXX devices have both volatile and nonvolatile (EEPROM) memory. Table 4-2 shows the volatile and non-volatile memory and their interaction due to a POR event.

There are five configuration bits in both the volatile and nonvolatile memory, the DAC registers in both the volatile and nonvolatile memory, and two volatile status bits. The DAC registers (volatile and nonvolatile) will be either 12 bits (MCP48FEB2X), 10 bits (MCP48FEB1X), or 8 bits (MCP48FEB0X) wide.

When the device is first powered-up, it automatically uploads the EEPROM memory values to the volatile memory. The volatile memory determines the analog output (V<sub>OUT</sub>) pin voltage. After the device is powered-up, the user can update the device memory.

The SPI interface is how this memory is read and written. Refer to **Section 6.0 "SPI Serial Interface Module"** and **Section 7.0 "SPI Commands"** for more details on reading and writing the device's memory.

When the nonvolatile memory is written, the device starts writing the EEPROM cell at the rising edge of the  $\overline{\text{CS}}$  pin.

Register 4-4 shows the operation of the device status bits, Table 4-1 and Table 4-3 show the operation of the device configuration bits, and Table 4-2 shows the factory default value of a POR/BOR event for the device configuration bits.

There are two status bits. These are only in volatile memory and give indication on the status of the device. The POR bit indicates if the device  $V_{DD}$  is above or below the POR trip point. During normal operation, this bit should be '1'. The EEWA bit indicates if an EEPROM write cycle is in progress. While the EEWA bit is low (during the EEPROM writing), all commands are ignored, except for the Read command.

NOTES:

# 6.0 SPI SERIAL INTERFACE MODULE

The MCP48FEBXX's SPI Serial Interface Module supports the SPI serial protocol specification. Figure 6-1 shows a typical SPI interface connection.

The command format and waveforms for the MCP48FEBXX is defined in **Section 7.0** "SPI Commands".

### 6.1 Overview

This sections discusses some of the specific characteristics of the MCP48FEBXX's Serial Interface Module.

The following sections discuss some of these device-specific characteristics:

- Communication Data Rates
- Communication Data Rates
- POR/BOR
- Interface Pins (CS, SCK, SDI, SDO, and LAT/HVC)

### 6.2 SPI SERIAL INTERFACE

The MCP48FEBXX devices support the SPI serial protocol. This SPI operates in slave mode (does not generate the serial clock).

The SPI interface uses up to four pins. These are:

- CS Chip Select
- · SCK Serial Clock
- · SDI Serial Data In
- · SDO Serial Data Out

An additional HVC pin is available for High Voltage command support. High Voltage commands allow the device to enable and disable nonvolatile configuration bits. Without high voltage present, those bits are inhibited from being modified.

Typical SPI Interfaces are shown in Figure 6-1. In the SPI interface, the Master's Output pin is connected to the Slave's Input pin, and the Master's Input pin is connected to the Slave's Output pin.

The MCP48FEBXX SPI's module supports two (of the four) standard SPI modes. These are Mode 0 , 0 and 1 , 1. The SPI mode is determined by the state of the SCK pin (V $_{IH}$  or V $_{IL}$ ) when the  $\overline{CS}$  pin transitions from inactive (V $_{IH}$ ) to active (V $_{IL}$ ).

The HVC pin is high-voltage tolerant. To enter a high voltage command, the HVC pin must be greater than the  $V_{IHH}$  voltage.

### 6.3 Communication Data Rates

The MCP48FEBXX supports clock rates (bit rate) of up to 20 MHz for write commands and 10 MHz for read commands.

For most applications, the write time will be considered more important, since that is how the device operation is controlled.

### 6.4 POR/BOR

On a POR/BOR event, the SPI Serial Interface Module state machine is reset, which includes that the Device's Memory Address pointer is forced to 00h.

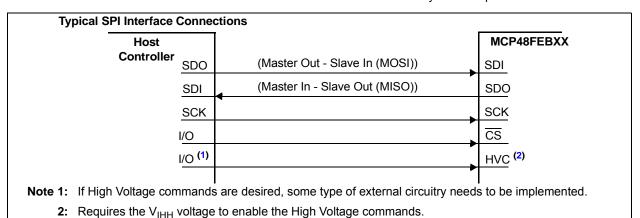


FIGURE 6-1: Typical SPI Interface Block Diagram.

# 6.5 Interface Pins (CS, SCK, SDI, SDO, and LAT/HVC)

The operation of the five interface pins and the High Voltage command (HVC) pin are discussed in this section. These pins are:

- · SDI (Serial Data In)
- · SDO (Serial Data Out)
- · SCK (Serial Clock)
- · CS (Chip Select)
- LAT/HVC (High Voltage command)

The serial interface works on either 8-bit or 24-bit boundaries depending on the selected command. The Chip Select ( $\overline{\text{CS}}$ ) pin frames the SPI commands.

### 6.5.1 SERIAL DATA IN (SDI)

The Serial Data In (SDI) signal is the data signal into the device. The value on this pin is latched on the rising edge of the SCK signal.

### 6.5.1.1 Serial Data Out (SDO)

The Serial Data Out (SDO) signal is the data signal out of the device. The value on this pin is driven on the falling edge of the SCK signal.

Once the  $\overline{\text{CS}}$  pin is forced to the active level (V<sub>IL</sub> or V<sub>IHH</sub>), the SDO pin will be driven. The state of the SDO pin is determined by the serial bit's position in the command, the command selected, and if there is a command error state (CMDERR).

## 6.5.1.2 Serial Clock (SCK) (SPI Frequency Of Operation)

The SPI interface is specified to operate up to 20 MHz. The actual clock rate depends on the configuration of the system and the serial command used. Table 6-1 shows the SCK frequency for different configurations.

TABLE 6-1: SCK FREQUENCY

TABLE O II. CONTINE QUEINO!							
		Command					
Memory Typ	oe Access	Read	Write, Enable, Disable				
Nonvolatile Memory	SDI, SDO	10 MHz	20 MHz (1,2)				
Volatile Memory	SDI, SDO	10 MHz	20 MHz <sup>(2)</sup>				

- **Note 1:** After a write command, the internal write cycle must complete before the next SPI command is received.
  - 2: This is a design goal. The SDO pin performance is believed to be the limiting factor.

### 6.5.1.3 The $\overline{\text{CS}}$ Signal

The Chip Select  $(\overline{CS})$  signal is used to select the device and frame a command sequence. To start a command, or sequence of commands, the  $\overline{CS}$  signal must transition from the inactive state  $(V_{IH})$  to an active state  $(V_{IL}$  or  $V_{IHH})$ .

After the  $\overline{\text{CS}}$  signal has gone active, the SDO pin is driven and the clock bit counter is reset.

**Note:** There is a required delay after the  $\overline{CS}$  pin goes active to the 1st edge of the SCK pin.

If an error condition occurs for an SPI command, then the Command byte's Command Error (CMDERR) bit (on the SDO pin) will be driven low (V<sub>IL</sub>). To exit the error condition, the user must take the  $\overline{\text{CS}}$  pin to the V<sub>IH</sub> level.

When the  $\overline{\text{CS}}$  pin returns to the inactive state (V<sub>IH</sub>), the SPI module resets (including the address pointer). While the  $\overline{\text{CS}}$  pin is in the inactive state (V<sub>IH</sub>), the serial interface is ignored. This allows the Host Controller to interface to other SPI devices using the same SDI, SDO, and SCK signals.

### 6.5.1.4 The HVC Signal

The high-voltage capability of the HVC pin allows High Voltage commands. High Voltage commands allow the device's WiperLock Technology and write protect features to be enabled and disabled.

#### 6.5.2 THE SPI MODES

The SPI module supports two (of the four) standard SPI modes. These are Mode 0, 0 and 1, 1. The mode is determined by the state of the SDI pin on the rising edge of the 1st clock bit (of the 8-bit byte).

### 6.5.2.1 Mode 0,0

### In **Mode 0,0**:

- SCK idle state = low (V<sub>II</sub>)
- Data is clocked in on the SDI pin on the rising edge of SCK
- Data is clocked out on the SDO pin on the falling edge of SCK

### 6.5.2.2 Mode 1,1

### In Mode 1,1:

- SCK idle state = high (V<sub>IH</sub>)
- Data is clocked in on the SDI pin on the rising edge of SCK
- Data is clocked out on the SDO pin on the falling edge of SCK

### 7.0 SPI COMMANDS

This section documents the commands that the device supports.

The MCP48FEBXX's SPI command format supports 32 memory address locations and four commands. Commands may have two modes. These are:

- · Normal Serial Commands
- · High-Voltage Serial Commands

The four commands are:

- Write command (C1:C0 = '00')
- Read command (C1:C0 = '11')
- Commands to Modify the Device Configuration Bits:

 $(HVC = V_{IHH})$ 

- Enable Configuration Bit (C1:C0 = '10')
- Disable Configuration Bit (C1:C0 = '01')

The supported commands are shown in Table 7-1. These commands allow for both single data or continuous data operation. Table 7-1 also shows the required number of bit clocks for each command's different mode of operation.

Normal Serial commands are those where the HVC pin is driven to either  $V_{IH}$  or  $V_{IL}$ . With High-Voltage Serial commands, the HVC pin is driven to  $V_{IHH}$ .

The 8-bit commands (see Figure 7-1) are used to modify the device Configuration bits (Enable Configuration Bit and Disable Configuration Bit), while the 24-bit commands (see Figure 7-2) are used to read and write to the device registers (Read Command and Write Command). These commands contain a Command Byte and two Data Bytes.

Table 7-2 shows an overview of all the SPI commands and their interaction with other device features.

TABLE 7-1: SPI COMMANDS - NUMBER OF CLOCKS

Command				# of Bit	Data Update Rate				
	Code			(1)	Clocks	(8-bit/10-bit/12-bit) (Data Words/Second)			Comments
Operation	C1	CO	HV	Mode <sup>(1)</sup>	(2)	@ 1 MHz	@ 10 MHz	@ 20 MHz <sup>(3)</sup>	1
Write Command	0	0	No <sup>(3)</sup>	Single	24	41,666	416,666	833,333	
	0	0	No <sup>(3)</sup>	Continuous	24 * n	41,666	416,666	833,333	For 10 data words
Read Command (4)	1	1	No <sup>(3)</sup>	Single	24	41,666	416,666	833,333	
	1	1	No <sup>(3)</sup>	Continuous	24 * n	41,666	416,666	833,333	For 10 data words
<b>Enable Configuration</b>	1	0	Yes	Single	8	125,000	1,250,000	2,500,000	
Bit Command	1	0	Yes	Continuous	8 * n	125,000	1,250,000	2,500,000	For 10 data words
<b>Disable Configuration</b>	0	1	Yes	Single	8	125,000	1,250,000	2,500,000	
Bit Command	0	1	Yes	Continuous	8 * n	125,000	1,250,000	2,500,000	For 10 data words

- **Note 1:** Nonvolatile registers can only use the "Single" mode.
  - 2: "n" indicates the number of times the command operation is to be repeated.
  - **3:** If the state of the HVC pin is V<sub>IHH</sub>, then the command is ignored, but a Command Error condition (CMDERR) will NOT be generated.
  - 4: This command is useful to determine when an EEPROM programming cycle has completed.

### 7.0.1 COMMAND BYTE

The command byte has three fields: the address, the command, and one data bit (see Figure 7-1). Currently only one of the data bits is defined (D8). This is for the Write command.

The device memory is accessed when the master sends a proper command byte to select the desired operation. The memory location getting accessed is contained in the command byte's AD4:AD0 bits. The action desired is contained in the command byte's C1:C0 bits, see Table 7-2. C1:C0 determines if the desired memory location will be read, written, enabled or disabled.

As the command byte is being loaded into the device (on the SDI pin), the device's SDO pin is driving. The SDO pin will output high bits for the first seven bits of that command. On the 8th bit, the SDO pin will output the CMDERR bit state (see Section 7.0.3 "Error Condition").

### 7.0.2 DATA BYTES

Data bytes are only present in the Read and the Write commands. These commands concatenate the two data bytes after the command byte, for a 24-bit long command (see Figure 7-1).

TABLE 7-2: COMMAND BIT OVERVIEW

C1:C0 Bit States	Command	# of Bits	Normal or HV	
11	Read Data	24-Bits	Normal	
00	Write Data	24-Bits	Normal	
01	Enable <sup>(1)</sup>	8-Bits	HV Only	
10	Disable (1)	8-Bits	HV Only	

Note 1: High Voltage enable and disable commands on select nonvolatile memory locations.

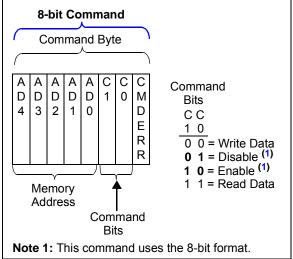


FIGURE 7-1: 8-BitSPICommandFormat.

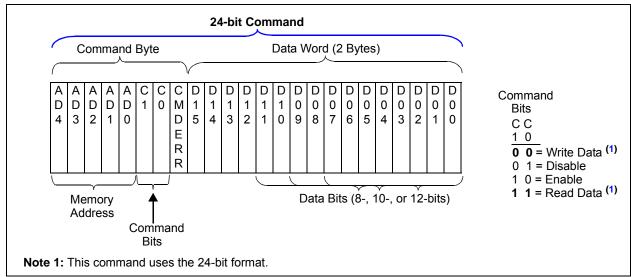


FIGURE 7-2: 24-bit SPI Command Format.

#### 7.0.3 ERROR CONDITION

The Command Error (CMDERR) bit indicates if the five address bits received (AD4:AD0) and the two command bits received (C1:C0) are a valid combination (see Figures 7-1 and 7-2). The CMDERR bit is high if the combination is valid and low if the combination is invalid.

The Command Error bit will also be low if a write to a nonvolatile address has been specified and another SPI command occurs before the  $\overline{\text{CS}}$  pin is driven inactive (V $_{\text{IH}}$ ).

SPI commands that do not have a multiple of eight clocks are ignored.

Once an error condition has occurred, any following commands are ignored. All following SDO bits will be low until the CMDERR condition is cleared by forcing the  $\overline{CS}$  pin to the inactive state (V<sub>IH</sub>).

### 7.0.3.1 Aborting a Transmission

All SPI transmissions must have the correct number of SCK pulses to be executed. The command is not executed until the complete number of clocks have been received. Some commands also require the  $\overline{\text{CS}}$  pin to be forced inactive (V<sub>IH</sub>). If the  $\overline{\text{CS}}$  pin is forced to the inactive state (V<sub>IH</sub>), the serial interface is reset. Partial commands are not executed.

SPI is more susceptible to noise than other bus protocols. The most likely case is that noise corrupts the value of the data being clocked into the MCP48FEBXX or the SCK pin is injected with extra clock pulses. This may cause data to be corrupted in the device, or a Command Error to occur, since the address and command bits were not a valid combination. The extra SCK pulse will also cause the SPI data (SDI) and clock (SCK) to be out of sync. Forcing the  $\overline{\text{CS}}$  pin to the inactive state (VIH) resets the serial interface. The SPI interface will ignore activity on the SDI and SCK pins until the  $\overline{\text{CS}}$  pin transition to the active state is detected (VIH to VIL or VIH to VIHH).

- Note 1: When data is not being received by the  $\frac{\text{MCP48FEBXX, it is recommended that the}}{\overline{\text{CS}} \text{ pin be forced to the inactive level (V}_{\text{IL}}).}$ 
  - 2: It is also recommended that long continuous command strings be broken down into single commands or shorter continuous command strings. This reduces the probability of noise on the SCK pin corrupting the desired SPI commands.

#### 7.0.4 CONTINUOUS COMMANDS

The device supports the <u>ability</u> to execute commands continuously. While the  $\overline{\text{CS}}$  pin is in the active state  $(V_{\text{IL}})$ , any sequence of valid commands may be received.

The following example is a valid sequence of events:

- CS pin driven active (V<sub>IL</sub>)
- 2. Read command
- 3. Write command (Volatile memory)
- 4. Write command (Nonvolatile memory)
- 5.  $\overline{CS}$  pin driven inactive (V<sub>IH</sub>)
  - **Note 1:** It is recommended that while the CS pin is active, only one type of command should be issued. When changing commands, it is advisable to take the  $\overline{\text{CS}}$  pin inactive then force it back to the active state.
    - 2: It is also recommended that long command strings should be broken down into shorter command strings. This reduces the probability of noise on the SCK pin, corrupting the desired SPI command string.

### 7.1 Write Command

Write commands are used to transfer data to the desired memory location (from the Host controller). The Write command can be issued to both the volatile and nonvolatile memory locations.

Write commands can be structured as either Single or Continuous.

The format of the command is shown in Figures 7-3 (Single) and 7-4 (Continuous).

A write command to a volatile memory location changes that location after a properly formatted write command has been received.

A write command to a nonvolatile memory location will start an EEPROM write cycle only after a properly formatted write command has been received and the  $\overline{\text{CS}}$  pin transitions to the inactive state ( $V_{\text{IH}}$ ).

- Note 1: Writes to certain memory locations will be dependent on the state of the WiperLock™ technology status bits.
  - 2: During device communication, if the Device Address/Command combination is invalid or an unimplemented Device Address is specified, then the MCP48FEBXX will generate a Command Error state. To reset the SPI state machine, the CS pin must transition to the inactive state (VIH).

## 7.1.1 SINGLE WRITE TO VOLATILE MEMORY

The write operation requires that the  $\overline{\text{CS}}$  pin be in the active state (V<sub>IL</sub>). Typically, the  $\overline{\text{CS}}$  pin will be in the inactive state (V<sub>IL</sub>) and is driven to the active state (V<sub>IL</sub>). The 24-bit Write command (Command Byte and Data Bytes) is then clocked in on the SCK and SDI pins. Once all 24 bits have been received, the specified volatile address is updated. A write will not occur if the Write command isn't exactly 24 clock pulses. This protects against system issues corrupting the nonvolatile memory locations.

Figures 7-5 and 7-6 show the waveforms for a single write (depending on SPI mode).

## 7.1.2 SINGLE WRITE TO NONVOLATILE MEMORY

The sequence to write to a single nonvolatile memory location is the same as a single write to volatile memory with the exception that after the  $\overline{\text{CS}}$  pin is driven inactive (V<sub>IH</sub>), the EEPROM write cycle (t<sub>WC</sub>) is started. A write cycle will not start if the Write command isn't exactly 24 clock pulses. This protects against system issues corrupting the nonvolatile memory locations.

Once a write command to a nonvolatile memory location has been received, no other SPI commands should be received before the  $\overline{\text{CS}}$  pin transitions to the inactive state (V<sub>IH</sub>), or the current SPI command will have a Command Error (CMDERR) occur.

After the CS pin is driven inactive ( $V_{IH}$ ), the serial interface may immediately be re-enabled by driving the  $\overline{CS}$  pin to the active state ( $V_{IL}$ ).

During an EEPROM write cycle, access to the volatile memory is allowed when using the appropriate command sequence. Commands that address nonvolatile memory are ignored until the EEPROM write cycle ( $t_{WC}$ ) completes. This allows the Host Controller to operate on the volatile DAC registers.

**Note:** The EEWA status bit indicates if an EEPROM write cycle is active (see Register 4-4).

Figures 7-5 and 7-6 show the waveforms for a single write (depending on the SPI mode).

## 7.1.3 CONTINUOUS WRITES TO VOLATILE MEMORY

A Continuous Write mode of operation is possible when writing to the device's volatile memory registers (see Table 7-3). Figure 7-4 shows the sequence for three continuous writes. The writes do not need to be to the same volatile memory address.

TABLE 7-3: VOLATILE MEMORY ADDRESSES

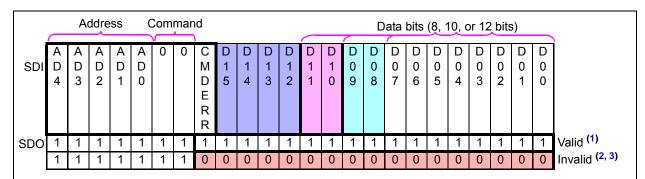
Address	Single-Channel	Dual-Channel
00h	Yes	Yes
01h	No	Yes
08h	Yes	Yes
09h	Yes	Yes
0Ah	Yes	Yes

## 7.1.4 CONTINUOUS WRITES TO NONVOLATILE MEMORY

Continuous writes to nonvolatile memory are not allowed, and attempts to do so will result in a Command Error (CMDERR) condition.

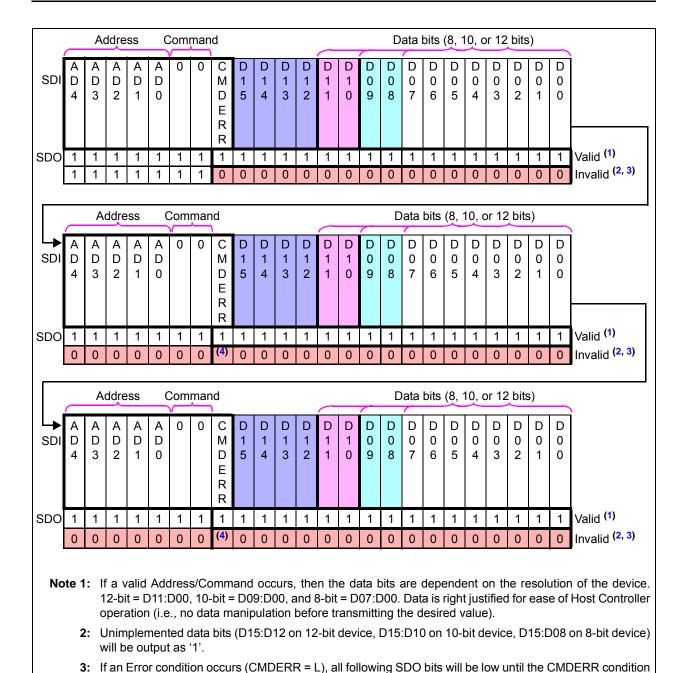
## 7.1.5 THE HIGH VOLTAGE COMMAND (HVC) SIGNAL

If the state of the HVC pin is  $V_{IHH}$ , then the command is ignored, but a Command Error condition (CMDERR) will NOT be generated.



- **Note 1:** If a valid Address/Command occurs, then the data bits are dependent on the resolution of the device. 12-bit = D11:D00, 10-bit = D09:D00, and 8-bit = D07:D00. Data is right justified for ease of Host Controller operation (i.e., no data manipulation before transmitting the desired value).
  - 2: Unimplemented data bits (D15:D12 on 12-bit device, D15:D10 on 10-bit device, D15:D08 on 8-bit device) will be output as '1'.
  - 3: If an Error condition occurs (CMDERR = L), all following SDO bits will be low until the CMDERR condition is cleared (the CS pin is forced to the inactive state).

FIGURE 7-3: Write Command - SDI and SDO States.



**4:** This CMDERR bit will be forced to '0', regardless if this Address+Command combination is valid. This command will not be completed and requires the  $\overline{CS}$  pin to return to  $V_{IH}$  to clear the CMDERR condition.

FIGURE 7-4: Continuous Write Sequence (Volatile Memory only).

is cleared (the  $\overline{CS}$  pin is forced to the inactive state).

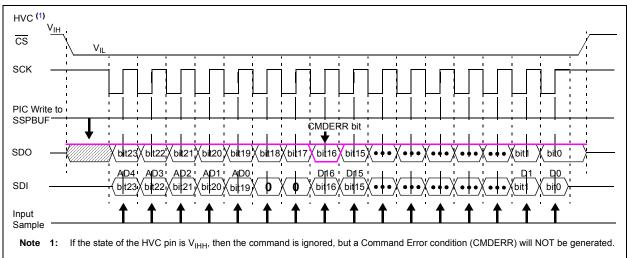


FIGURE 7-5: 24-Bit Write Command (C1:C0 = "00") - SPI Waveform with PIC MCU (Mode 1,1).

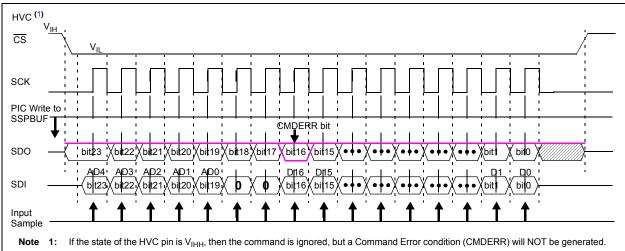


FIGURE 7-6: 24-Bit Write Command (C1:C0 = "00") - SPI Waveform with PIC MCU (Mode 0,0).

### 7.2 Read Command

The Read command is a 24-bit command and is used to transfer data from the specified memory location to the Host controller. The Read command can be issued to both the volatile and nonvolatile memory locations. The format of the command as well as an example SDI and SDO data is shown in Figure 7-7.

The first 7-bits of the Read command determine the address and the command. The 8th clock will output the CMDERR bit on the SDO pin. By means of the remaining 16 clocks, the device will transmit the data bits of the specified address (AD4:AD0).

During an EEPROM write cycle (write to nonvolatile memory location or <code>Enable/Disable Configuration Bit command</code>), the Read command can only read the volatile memory locations. By reading the Status Register (OAh), the Host Controller can determine when the write cycle has completed (via the state of the EEWA bit)

The Read command formats include:

- Single Read
- Continuous Reads

- Note 1: During device communication, if the Device Address/Command combination is invalid or an unimplemented Address is specified, then the MCP48FEBXX will command error that byte. To reset the SPI state machine, the  $\overline{\text{CS}}$  pin must be driven to the V $_{\text{IH}}$  state.
  - **2:** If the LAT pin is High (V<sub>IH</sub>), reads of the volatile DAC Register read the output value, not the internal register.
  - 3: The read commands operate the same regardless of the state of the High-Voltage Command (HVC) signal.

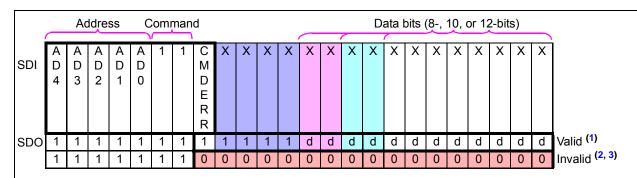
### 7.2.1 LAT PIN INTERACTION

During a Read command of the DACx Registers, if the LAT pin transitions from  $V_{IH}$  to  $V_{IL}$ , then the read data may be corrupted. This is due to the fact that the data being read is the output value and not the DAC register value. The LAT pin transition causes an update of the output value. Based on the DAC output value, the DACx register value, and the Command bit where the LAT pin transitions, the value being read could be corrupted.

If LAT pin transitions occur during a read of the DACx register, it is recommended that sequential reads be performed until the two most recent read values match. Then the most recent read data is good.

### 7.2.2 SINGLE READ

The Read command operation requires that the  $\overline{\text{CS}}$  pin be in the active state  $(V_{IL})$ . Typically, the  $\overline{\text{CS}}$  pin will be in the inactive state  $(V_{IH})$  and is driven to the active state  $(V_{IL})$ . The 24-bit Read command (Command Byte and Data Byte) is then clocked in on the SCK and SDI pins. The SDO pin starts driving data on the 8th bit (CMDERR bit), and the addressed data comes out on the 9th through 24th clocks.



- **Note 1:** If a valid Address/Command occurs, then the data bits are dependent on the resolution of the device. 12-bit = D11:D00, 10-bit = D09:D00, and 8-bit = D07:D00. Data is right justified for ease of Host Controller operation (i.e., no data manipulation before transmitting the desired value).
  - 2: Unimplemented data bits (D15:D12 on 12-bit device, D15:D10 on 10-bit device, D15:D08 on 8-bit device) will be output as '1'.
  - 3: If an Error condition occurs (CMDERR = L), all following SDO bits will be low until the CMDERR condition is cleared (the CS pin is forced to the inactive state).

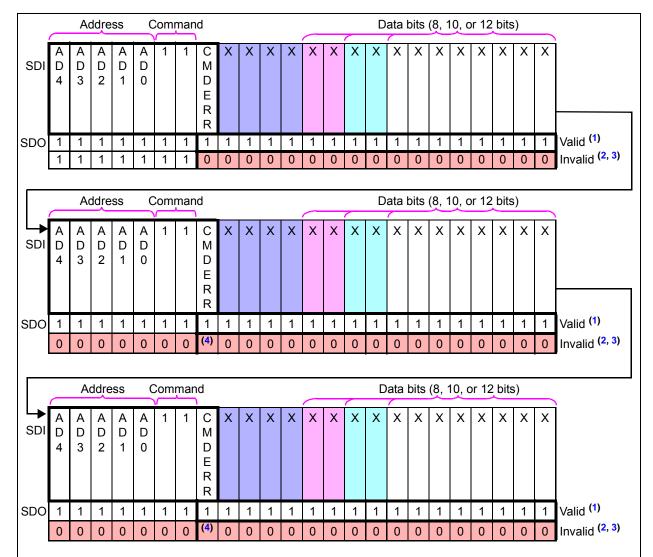
FIGURE 7-7: Read Command - SDI and SDO States.

### 7.2.3 CONTINUOUS READS

Continuous-reads format allows the device's memory to be read quickly. Continuous reads are possible to all memory locations. If a nonvolatile memory write cycle is occurring, then read commands may only access the volatile memory locations.

Figure 7-8 shows the sequence for three continuous reads. The reads do not need to be to the same memory address.

This is useful in reading the System Status register (0Ah) to determine if an EEPROM write cycle has completed (EEWA bit).



- **Note 1:** If a valid Address/Command occurs, then the data bits are dependent on the resolution of the device. 12-bit = D11:D00, 10-bit = D09:D00, and 8-bit = D07:D00. Data is right justified for ease of Host Controller operation (i.e., no data manipulation before transmitting the desired value).
  - 2: Unimplemented data bits (D15:D12 on 12-bit device, D15:D10 on 10-bit device, D15:D08 on 8-bit device) will be output as '1'.
  - 3: If an Error condition occurs (CMDERR = L), all following SDO bits will be low until the CMDERR condition is cleared (the CS pin is forced to the inactive state).
  - **4:** This CMDERR bit will be forced to '0', regardless if this Address+Command combination is valid. This command will not be completed and requires the  $\overline{CS}$  pin to return to  $V_{IH}$  to clear the CMDERR condition.

FIGURE 7-8: Continuous-Reads Sequence.

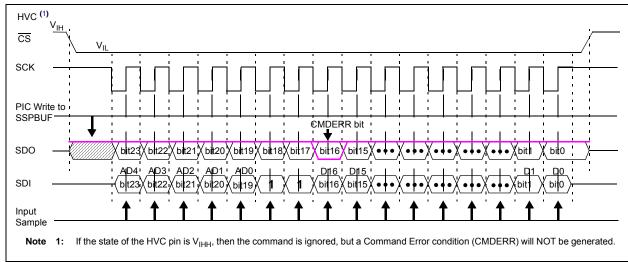


FIGURE 7-9: 24-Bit Read Command (C1:C0 = "11") - SPI Waveform with PIC MCU (Mode 1,1).

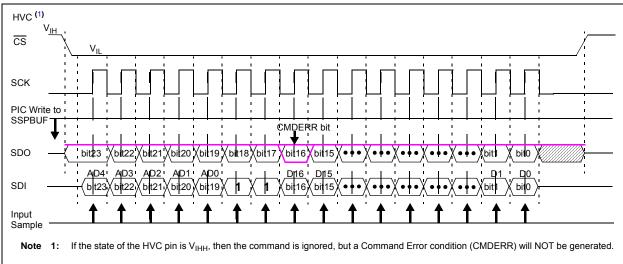


FIGURE 7-10: 24-Bit Read Command (C1:C0 = "11") - SPI Waveform with PIC MCU (Mode 0,0).

# 7.3 Commands to Modify the Device Configuration Bits

The MCP48FEBXX devices support two commands which are used to program the device's configuration bits. These commands require a high voltage ( $V_{IHH}$ ) on the HVC pin. These commands are:

- Enable Configuration Bit
- Disable Configuration Bit

The configuration bits are used to inhibit the DAC values from inadvertent modification. High voltage is required to change the state of these bits if/when the DAC values need to be modified.

# 7.4 Enable Configuration Bit (High Voltage)

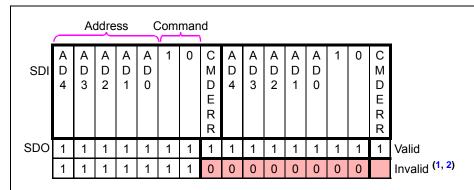
Figure 7-11 (Enable) shows the formats for a single Enable Configuration Bit command. The command will only start the EEPROM write cycle ( $t_{WC}$ ) after a properly formatted command has been received.

During an EEPROM write cycle, only serial commands to volatile memory are accepted. All other serial commands are ignored until the EEPROM write cycle ( $t_{WC}$ ) completes. This allows the Host Controller to operate on the volatile DAC, the volatile  $V_{REF}$ , Power-Down, Gain and Status, and WiperLock Technology Status registers. The EEWA bit in the Status register indicates the status of the EEPROM write cycle.

## 7.4.1 HIGH-VOLTAGE COMMAND (HVC) SIGNAL

The High-Voltage Command (HVC) signal is used to indicate that the command, or sequence of commands, are in the High-Voltage mode. Signals higher than  $V_{IHH}$  (~9.0V) on the  $\overline{LAT}/HVC$  pin puts the device into High-Voltage mode. High-Voltage commands allow the device's WiperLock technology and write-protect features to be enabled and disabled.

**Note 1:** There is a required delay after the HVC pin is driven to the V<sub>IHH</sub> level on the 1st edge of the SCK pin.



- Note 1: If an Error condition occurs (CMDERR = L), all following SDO bits will be low until the CMDERR condition is cleared (the CS pin is forced to the inactive state).
  - 2: This CMDERR bit will be forced to '0', regardless if this Address+Command combination is valid. This command will not be completed and requires the CS pin to return to V<sub>IH</sub> to clear the CMDERR condition.

FIGURE 7-11: Enable Command Sequence.

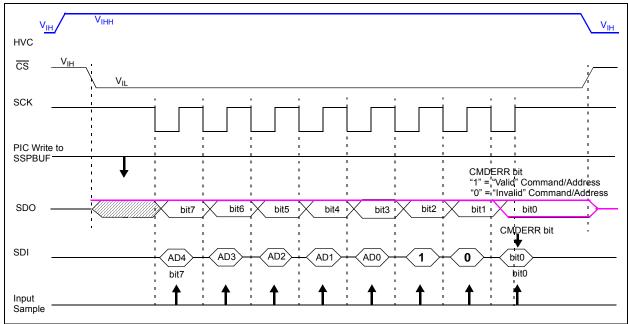


FIGURE 7-12: 8-Bit Enable Command (C1:C0 = "10") - SPI Waveform with PIC MCU (Mode 1,1).

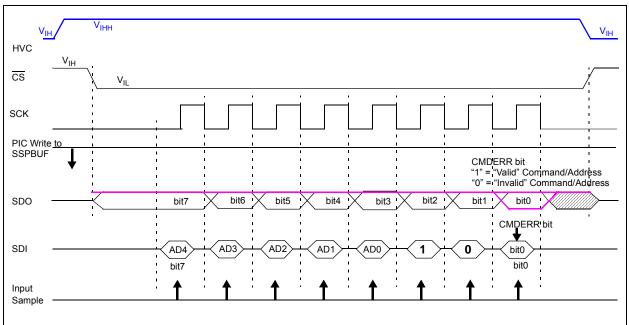


FIGURE 7-13: 8-Bit Enable Command (C1:C0 = "10") - SPI Waveform with PIC MCU (Mode 0,0).

# 7.5 Disable Configuration Bit (High Voltage)

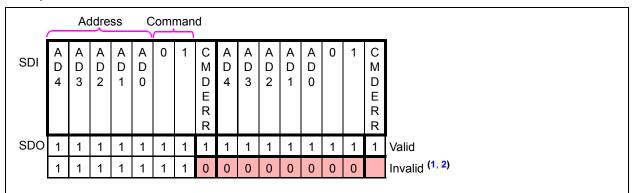
Figure 7-14 (Disable) shows the formats for a single Disable Configuration Bit command. The command will only start an EEPROM write cycle ( $t_{WC}$ ) after a properly formatted command has been received.

During an EEPROM write cycle, only serial commands to volatile memory are accepted. All other serial commands are ignored until the EEPROM write cycle ( $t_{WC}$ ) completes. This allows the Host Controller to operate on the volatile DAC, the volatile  $V_{REF}$ , Power-Down, Gain and Status, and WiperLock Technology Status registers. The EEWA bit in the Status register indicates the status of an EEPROM write cycle.

## 7.5.1 HIGH-VOLTAGE COMMAND (HVC) SIGNAL

The High-Voltage Command (HVC) signal is used to indicate that the command, or sequence of commands, are in the High-Voltage mode. Signals higher than  $V_{IHH}$  (~9.0V) on the HVC pin puts the MCP48FEBXX devices into High-Voltage mode. High Voltage commands allow the device's WiperLock technology and write protect features to be enabled and disabled.

**Note 1:** There is a required delay after the HVC pin is driven to the V<sub>IHH</sub> level to the 1st edge of the SCK pin.



- **Note 1:** If an Error condition occurs (CMDERR = L), all following SDO bits will be low until the CMDERR condition is cleared (the  $\overline{\text{CS}}$  pin is forced to the inactive state).
  - 2: This CMDERR bit will be forced to '0', regardless if this Address+Command combination is valid. This command will not be completed and requires the  $\overline{CS}$  pin to return to  $V_{IH}$  to clear the CMDERR condition.

FIGURE 7-14: Disable Command Sequence.

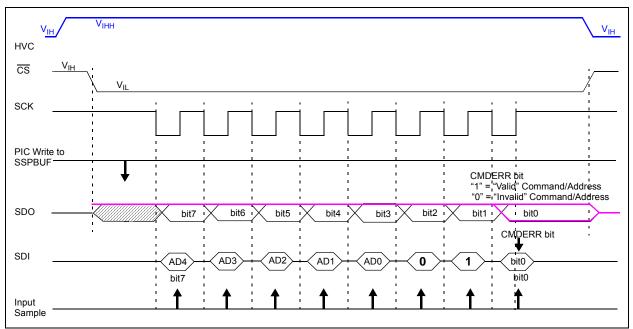


FIGURE 7-15: 8-Bit Disable Command (C1:C0 = "01") - SPI Waveform with PIC MCU (Mode 1,1).

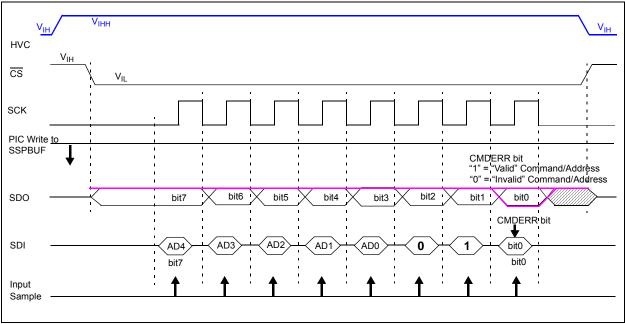


FIGURE 7-16: 8-Bit Disable Command (C1:C0 = "01") - SPI Waveform with PIC MCU (Mode 0,0).

### 8.0 TYPICAL APPLICATIONS

The MCP48FEBXX family of devices are general purpose, single/dual-channel voltage output DACs for various applications where a precision operation with low power and nonvolatile EEPROM memory is needed.

Since the devices include a nonvolatile EEPROM memory, the user can utilize these devices for applications that require the output to return to the previous setup value on subsequent power-ups.

Applications generally suited for the devices are:

- · Set Point or Offset Trimming
- · Sensor Calibration
- · Portable Instrumentation (Battery-Powered)
- Motor Control

### 8.1 Power Supply Considerations

The power source should be as clean as possible. The power supply to the device is also used for the DAC voltage reference internally if the internal  $V_{DD}$  is selected as the resistor ladder's reference voltage (VRxB:VRxA = '00').

Any noise induced on the  $V_{DD}$  line can affect the DAC performance. Typical applications will require a bypass capacitor in order to filter out high-frequency noise on the  $V_{DD}$  line. The noise can be induced onto the power supply's traces or as a result of changes on the DAC output. The bypass capacitor helps to minimize the effect of these noise sources on signal integrity. Figure 8-1 shows an example of using two bypass capacitors (a 10  $\mu F$  tantalum capacitor and a 0.1  $\mu F$  ceramic capacitor) in parallel on the  $V_{DD}$  line. These capacitors should be placed as close to the  $V_{DD}$  pin as possible (within 4 mm). If the application circuit has separate digital and analog power supplies, the  $V_{DD}$  and  $V_{SS}$  pins of the device should reside on the analog plane.

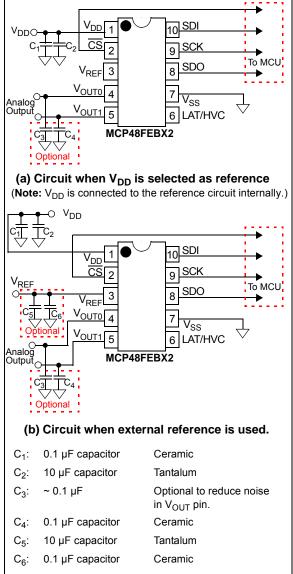


FIGURE 8-1: Bypass Filtering Example Circuit.

### 8.2 Application Examples

The MCP48FEBXX devices are rail-to-rail output DACs designed to operate with a  $V_{DD}$  range of 2.7V to 5.5V. The internal output operational amplifier is robust enough to drive common, small-signal loads directly, thus eliminating the cost and size of external buffers for most applications. The user can use gain of 1 or 2 of the output operational amplifier by setting the Configuration register bits. Also, the user can use internal  $V_{DD}$  as the reference or use an external reference. Various user options and easy-to-use features make the devices suitable for various modern DAC applications.

Application examples include:

- · Decreasing Output Step Size
- · Building a "Window" DAC
- · Bipolar Operation
- · Selectable Gain and Offset Bipolar Voltage Output
- · Designing a Double-Precision DAC
- · Building Programmable Current Source
- · Serial Interface Communication Times
- · Power Supply Considerations
- · Layout Considerations

### 8.2.1 DC SET POINT OR CALIBRATION

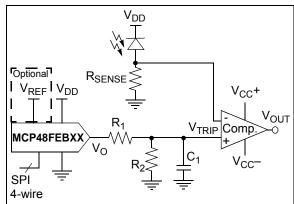
A common application for the devices is a digitally-controlled set point and/or calibration of variable parameters, such as sensor offset or slope. For example, the MCP48FEB2X provides 4096 output steps. If voltage reference is 4.096V (where Gx = '0'), the LSb size is 1 mV. If a smaller output step size is desired, a lower external voltage reference is needed.

### 8.2.1.1 Decreasing Output Step Size

If the application is calibrating the bias voltage of a diode or transistor, a bias voltage range of 0.8V may be desired with about  $200~\mu V$  resolution per step. Two common methods to achieve small step size are:

- Using Lower V<sub>ref</sub> Pin Voltage: Using an external voltage reference (V<sub>REF</sub>) is an option if the external reference is available with the desired output voltage range. However, occasionally, when using a low-voltage reference voltage, the noise floor causes a SNR error that is intolerable.
- Using A Voltage Divider On The DAC's Output:
   Using a voltage divider provides some
   advantages when external voltage reference
   needs to be very low or when the desired output
   voltage is not available. In this case, a larger
   value reference voltage is used while two
   resistors scale the output range down to the
   precise desired level.

Figure 8-2 illustrates this concept. A bypass capacitor on the output of the voltage divider plays a critical function in attenuating the output noise of the DAC and the induced noise from the environment.



**FIGURE 8-2:** Example Circuit Of Set Point or Threshold Calibration.

## EQUATION 8-1: V<sub>OUT</sub> AND V<sub>TRIP</sub> CALCULATIONS

$$V_{OUT} = V_{REF} \cdot G \cdot \frac{DAC \ Register \ Value}{2^{N}}$$

$$V_{trip} = V_{OUT} \left(\frac{R_{2}}{R_{1} + R_{2}}\right)$$

### 8.2.1.2 Building a "Window" DAC

When calibrating a set point or threshold of a sensor, typically only a small portion of the DAC output range is utilized. If the LSb size is adequate enough to meet the application's accuracy needs, the unused range is sacrificed without consequences. If greater accuracy is needed, then the output range will need to be reduced to increase the resolution around the desired threshold.

If the threshold is not near  $V_{REF}$ ,  $2 \cdot V_{REF}$ , or  $V_{SS}$ , then creating a "window" around the threshold has several advantages. One simple method to create this "window" is to use a voltage divider network with a pull-up and pull-down resistor. Figure 8-3 and Figure 8-5 illustrate this concept.

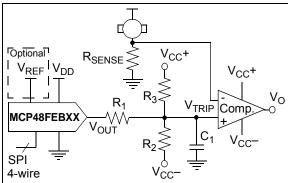


FIGURE 8-3: Single-Supply "Window"
DAC.

# EQUATION 8-2: V<sub>OUT</sub> AND V<sub>TRIP</sub> CALCULATIONS

$$V_{OUT} = V_{REF} \bullet G \bullet \frac{DAC\ Register\ Value}{2^N}$$

$$V_{TRIP} = \frac{V_{OUT}R_{23} + V_{23}R_1}{R_1 + R_{23}}$$

$$R_{23} = \frac{R_2R_3}{R_2 + R_3}$$

$$V_{23} = \frac{(V_{CC+}R_2) + (V_{CC}.R_3)}{R_2 + R_3}$$

$$V_{OUT} \longrightarrow V_{TRIP}$$

$$R_{23}$$

### 8.3 Bipolar Operation

Bipolar operation is achievable by utilizing an external operational amplifier. This configuration is desirable due to the wide variety and availability of op amps. This allows a general purpose DAC, with its cost and availability advantages, to meet almost any desired output voltage range, power and noise performance.

Figure 8-4 illustrates a simple bipolar voltage source configuration.  $R_1$  and  $R_2$  allow the gain to be selected, while  $R_3$  and  $R_4$  shift the DAC's output to a selected offset. Note that R4 can be tied to  $V_{DD}$  instead of  $V_{SS}$  if a higher offset is desired.

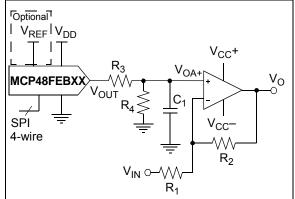


FIGURE 8-4: Digitally-Controlled Bipolar Voltage Source Example Circuit.

# EQUATION 8-3: $V_{OUT}$ , $V_{OA+}$ , AND $V_{O}$ CALCULATIONS

$$V_{OUT} = V_{REF} \cdot G \cdot \frac{DAC \ Register \ Value}{2^N}$$

$$V_{OA+} = \frac{V_{OUT} \cdot R_4}{R_3 + R_4}$$

$$V_O = V_{OA+} \cdot (I + \frac{R_2}{R_1}) \cdot V_{DD} \cdot (\frac{R_2}{R_1})$$

# 8.4 Selectable Gain and Offset Bipolar Voltage Output

In some applications, precision digital control of the output range is desirable. Figure 8-5 illustrates how to use DAC devices to achieve this in a bipolar or single-supply application.

This circuit is typically used for linearizing a sensor whose slope and offset varies.

The equation to design a bipolar "window" DAC would be utilized if  $R_3$ ,  $R_4$  and  $R_5$  are populated.

### **Bipolar DAC Example**

An output step size of 1 mV with an output range of ±2.05V is desired for a particular application.

**Step 1:** Calculate the range: +2.05V - (-2.05V) = 4.1V.

**Step 2:** Calculate the resolution needed: 4.1V/1 mV = 4100

Since  $2^{12}$  = 4096, 12-bit resolution is desired.

Step 3: The amplifier gain  $(R_2/R_1)$ , multiplied by full-scale  $V_{OUT}$  (4.096V), must be equal to the desired minimum output to achieve bipolar operation. Since any gain can be realized by choosing resistor values  $(R_1+R_2)$ , the  $V_{REF}$  value must be selected first. If a  $V_{REF}$  of 4.096V is used, solve for the amplifier's gain by setting the DAC to 0, knowing that the output needs to be -2.05V.

The equation can be simplified to:

### **EQUATION 8-4:**

$$\frac{-R_2}{R_1} = \frac{-2.05}{4.096V} \qquad \qquad \frac{R_2}{R_1} = \frac{1}{2}$$

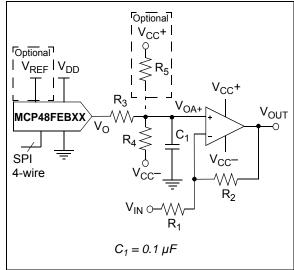
If  $R_1 = 20 \text{ k}\Omega$  and  $R_2 = 10 \text{ k}\Omega$ , the gain will be 0.5.

Step 4: Next, solve for  $R_3$  and  $R_4$  by setting the DAC to 4096, knowing that the output needs to be +2.05V.

### **EQUATION 8-5:**

$$\frac{R_4}{(R_3+R_4)} \,=\, \frac{2.05V + (0.5 \cdot 4.096V)}{I.5 \cdot 4.096V} \,=\, \frac{2}{3}$$

If  $R_4 = 20 \text{ k}\Omega$ , then  $R_3 = 10 \text{ k}\Omega$ 



**FIGURE 8-5:** Bipolar Voltage Source with Selectable Gain and Offset.

## EQUATION 8-6: V<sub>OUT</sub>, V<sub>OA+</sub>, AND V<sub>O</sub> CALCULATIONS

$$V_{OUT} = V_{REF} \bullet G \bullet \frac{DAC \ Register \ Value}{2^N}$$

$$V_{OA+} = \frac{V_{OUT} \bullet R_4 + V_{CC-} \bullet R_5}{R_3 + R_4}$$

$$V_O = \underbrace{V_{OA+} \bullet (1 + \frac{R_2}{R_I}) - V_{IN} \bullet (\frac{R_2}{R_I})}_{\text{Offset Adjust}}$$
Gain Adjust

# EQUATION 8-7: BIPOLAR "WINDOW" DAC USING $R_4$ AND $R_5$

Thevenin Equivalent 
$$V_{45} = \frac{V_{CC+}R_4 + V_{CC-}R_5}{R_4 + R_5}$$
 
$$V_{IN+} = \frac{V_{OUT}R_{45} + V_{45}R_3}{R_3 + R_{45}}$$
 
$$R_{45} = \frac{R_4R_5}{R_4 + R_5}$$
 
$$V_O = V_{IN+} \left(I + \frac{R_2}{R_I}\right) - V_A \left(\frac{R_2}{R_I}\right)$$
 Offset Adjust Gain Adjust

# 8.5 Designing a Double-Precision DAC

Figure 8-6 shows an example design of a single-supply voltage output capable of up to 24-bit resolution. This requires two 12-bit DACs. This design is simply a voltage divider with a buffered output.

#### **Double-Precision DAC Example**

If a similar application to the one developed in Bipolar DAC Example required a resolution of 1  $\mu$ V instead of 1 mV and a range of 0V to 4.1V, then 12-bit resolution would not be adequate.

Step 1: Calculate the resolution needed:  $4.1\text{V}/1~\mu\text{V} = 4.1~\text{x}~10^6.$  Since  $2^{22}$  = 4.2 x  $10^6$ , 22-bit resolution is desired. Since DNL = ±1.0 LSb, this design

can be attempted with the 12-bit DAC.

Step 2: Since DAC1's  $V_{OUT1}$  has a resolution of 1 mV, its output only needs to be "pulled" 1/1000 to meet the 1  $\mu$ V target. Dividing  $V_{OUT0}$  by 1000 would allow the application to compensate for DAC1's DNL error.

**Step 3:** If  $R_2$  is  $100\Omega$ , then  $R_1$  needs to be  $100 \text{ k}\Omega$ .

**Step 4:** The resulting transfer function is shown in the equation of Example 8-8.

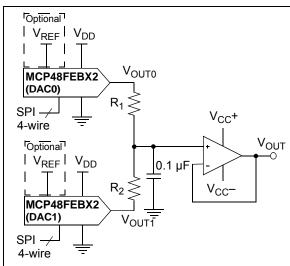


FIGURE 8-6: Simple Double-Precision DAC using MCP48FEBX2.

# **EQUATION 8-8: VOUT CALCULATION**

$$V_{OUT} = \begin{array}{c} V_{OUT0} \bullet R_2 + V_{OUT1} \bullet R_I \\ R_I + R_2 \end{array}$$

Where:

 $V_{OUT0}$  = ( $V_{REF} \cdot G \cdot DAC0 Register Value)/4096$ 

 $V_{OUT1} = (V_{REF} \cdot G \cdot DAC1 Register Value)/4096$ 

Gx = Selected Op Amp Gain

# 8.6 Building Programmable Current Source

Figure 8-7 shows an example of building a programmable current source using a voltage follower. The current sensor resistor is used to convert the DAC voltage output into a digitally-selectable current source.

The smaller R<sub>SENSE</sub> is, the less power dissipated across it. However, this also reduces the resolution that the current can be controlled.

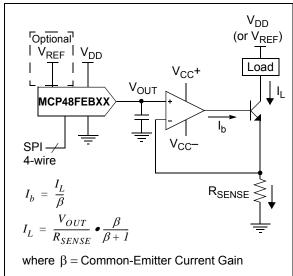


FIGURE 8-7: Digitally-Controlled Current Source.

# 8.7 Serial Interface Communication Times

Table 8-1 shows time/frequency of the supported operations of the SPI serial interface for the different serial interface operational frequencies. This, along with the  $V_{OUT}$  output performance (such as slew rate), would be used to determine your application's volatile DAC register update rate.

TABLE 8-1: SERIAL INTERFACE TIMES / FREQUENCIES

Command					Data Update F				
Code			# of Bit Clocks	(8-bit/10-bit/12-bit) (Data Words/Second)			Comments		
Operation	C 1	C 0	HV	Mode <sup>(1)</sup>	(2)	1 MHz	10 MHz	20 MHz <sup>(3)</sup>	
Write Command	0	0	No <sup>(4)</sup>	Single	24	41,666	416,666	833,333	
	0	0	No <sup>(4)</sup>	Continuous	24n	41,666	416,666	833,333	For 10 data words
Read Command (5)	1	1	No <sup>(4)</sup>	Single	24	41,666	416,666	N.A.	
	1	1	No <sup>(4)</sup>	Continuous	24n	41,666	416,666	N.A.	For 10 data words
Enable Configuration	1	0	Yes	Single	8	125,000	1,250,000	2,500,000	
Bit Command	1	0	Yes	Continuous	8n	125,000	1,250,000	2,500,000	For 10 data words
Disable Configuration	0	1	Yes	Single	8	125,000	1,250,000	2,500,000	
Bit Command	0	1	Yes	Continuous	8n	125,000	1,250,000	2,500,000	For 10 data words

- **Note 1:** Nonvolatile registers can only use the "Single" mode.
  - 2: "n" indicates the number of times the command operation is to be repeated.
  - **3:** Write command only.
  - 4: If the state of the HVC pin is  $V_{IHH}$ , then the command is ignored, but a Command Error condition (CMDERR) will NOT be generated
  - 5: This command is useful to determine when an EEPROM programming cycle has completed.

### 8.8 Design Considerations

In the design of a system with the MCP48FEBXX devices, the following considerations should be taken into account:

- Power Supply Considerations
- Layout Considerations

# 8.8.1 POWER SUPPLY CONSIDERATIONS

The typical application will require a bypass capacitor in order to filter high-frequency noise which can be induced onto the power supply's traces. The bypass capacitor helps to minimize the effect of these noise sources on signal integrity. Figure 8-8 illustrates an appropriate bypass strategy.

In this example, the recommended bypass capacitor value is 0.1  $\mu$ F. This capacitor should be placed as close (within 4 mm) to the device power pin (V<sub>DD</sub>) as possible.

The power source supplying these devices should be as clean as possible. If the application circuit has separate digital and analog power supplies,  $V_{DD}$  and  $V_{SS}$  should reside on the analog plane.

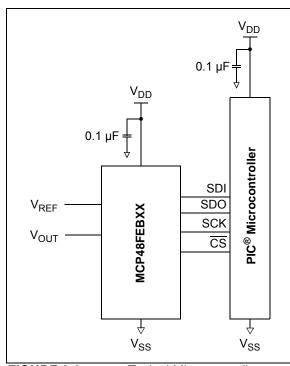


FIGURE 8-8: Connections.

Typical Microcontroller

#### 8.8.2 LAYOUT CONSIDERATIONS

Several layout considerations may be applicable to your application. These may include:

- Noise
- PCB Area Requirements

#### 8.8.2.1 Noise

Inductively-coupled AC transients and digital switching noise can degrade the input and output signal integrity, potentially masking the MCP48FEBXX's performance. Careful board layout minimizes these effects and increases the Signal-to-Noise Ratio (SNR). Multi-layer boards utilizing a low-inductance ground plane, isolated inputs, isolated outputs and proper decoupling are critical to achieving the performance that the silicon is capable of providing. Particularly harsh environments may require shielding of critical signals.

Separate digital and analog ground planes are recommended. In this case, the  $V_{SS}$  pin and the ground pins of the  $V_{DD}$  capacitors should be terminated to the analog ground plane.

Note:	Breadboards	and	wire-wrapped	boards	
	are not recommended.				

### 8.8.2.2 PCB Area Requirements

In some applications, PCB area is a criteria for device selection. Table 8-2 shows the typical package dimensions and area for the different package options.

TABLE 8-2: PACKAGE FOOTPRINT<sup>(1)</sup>

	Packag	je	Package Footprint			
Pins	Туре	Code	Dimen (mı		Area (mm²)	
<u>.                                    </u>			Length	Width		
10	MSOP	UN	3.00	4.90	14.70	

Note 1: Does not include recommended land pattern dimensions. Dimensions are typical values.

**NOTES:** 

### 9.0 DEVELOPMENT SUPPORT

Development support can be classified into two groups. These are:

- Development Tools
- Technical Documentation

### 9.1 Development Tools

The MCP48FEBXX devices currently do not have any development tools or bond-out boards. Please visit the Device's web product page (Development Tools tab) for the development tools availability after the release of this data sheet.

### 9.2 Technical Documentation

Several additional technical documents are available to assist you in your design and development. These technical documents include Application Notes, Technical Briefs, and Design Guides. Table 9-1 shows some of these documents.

TABLE 9-1: TECHNICAL DOCUMENTATION

Application Note Number	Title	Literature #
AN1326	Using the MCP4728 12-Bit DAC for LDMOS Amplifier Bias Control Applications	DS01326
_	Signal Chain Design Guide	DS21825
	Analog Solutions for Automotive Applications Design Guide	DS01005

NOTES:

#### 10.0 **PACKAGING INFORMATION**

#### 10.1 **Package Marking Information**

10-Lead MSOP





Example

Device Number	Code	Device Number	Code
MCP48FEB01-E/UN	48FE01	MCP48FEB02-E/UN	48FE02
MCP48FEB01T-E/UN	48FE01	MCP48FEB02T-E/UN	48FE02
MCP48FEB11-E/UN	48FE11	MCP48FEB12-E/UN	48FE12
MCP48FEB11T-E/UN	48FE11	MCP48FEB12T-E/UN	48FE12
MCP48FEB21-E/UN	48FE21	MCP48FEB22-E/UN	48FE22
MCP48FEB21T-E/UN	48FE21	MCP48FEB22T-E/UN	48FE22

Customer-specific information Legend: XX...X

Year code (last digit of calendar year) ΥY Year code (last 2 digits of calendar year) Week code (week of January 1 is week '01') WW

NNN

Alphanumeric traceability code
Pb-free JEDEC® designator for Matte Tin (Sn) (e3)

This package is Pb-free. The Pb-free JEDEC designator (@3)

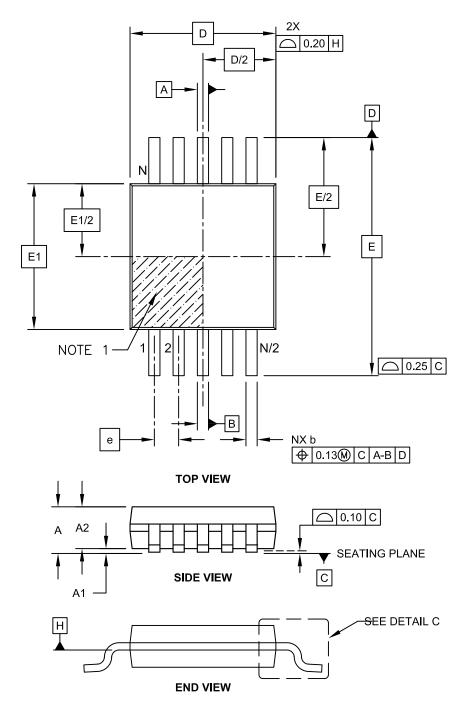
can be found on the outer packaging for this package.

In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available

characters for customer-specific information.

# 10-Lead Plastic Micro Small Outline Package (UN) [MSOP]

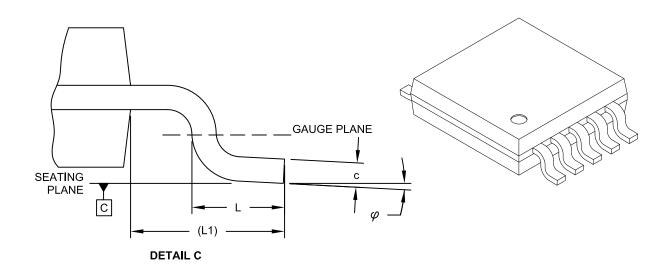
**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing C04-021C Sheet 1 of 2

### 10-Lead Plastic Micro Small Outline Package (UN) [MSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	MILLIMETERS					
Dimension	Limits	MIN	NOM	MAX		
Number of Pins	N		10			
Pitch	е		0.50 BSC			
Overall Height	Α	-	-	1.10		
Molded Package Thickness	A2	0.75	0.85	0.95		
Standoff	A1	0.00	-	0.15		
Overall Width	Е		4.90 BSC			
Molded Package Width	E1		3.00 BSC			
Overall Length	D		3.00 BSC			
Foot Length	L	0.40	0.60	0.80		
Footprint	L1	0.95 REF				
Foot Angle	$\varphi$	0°	-	8°		
Lead Thickness	С	0.08	-	0.23		
Lead Width	b	0.15	-	0.33		

#### Notes

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
- 3. Dimensioning and tolerancing per ASME Y14.5M.

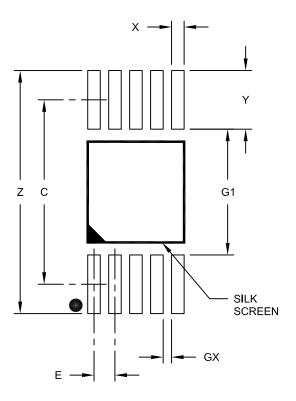
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-021C Sheet 2 of 2

# 10-Lead Plastic Micro Small Outline Package (UN) [MSOP]

**ote:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



**RECOMMENDED LAND PATTERN** 

	MILLIMETERS			
Dimension	MIN	NOM	MAX	
Contact Pitch	Е		0.50 BSC	
Contact Pad Spacing	С		4.40	
Overall Width	Z			5.80
Contact Pad Width (X10)	X1			0.30
Contact Pad Length (X10)	Y1			1.40
Distance Between Pads	G1	3.00		
Distance Between Pads	GX	0.20		

# Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2021A

# **APPENDIX A: REVISION HISTORY**

# **Revision B (September 2015)**

• Fixed a header/part number typographical error.

# **Revision A (September 2015)**

• Original release of this document.

### APPENDIX B: TERMINOLOGY

### **B.1** Resolution

Resolution is the number of DAC output states that divide the full-scale range. For the 12-bit DAC, the resolution is  $2^{12}$ , meaning the DAC code ranges from 0 to 4095.

Note: When there are  $2^N$  resistors in the resistor ladder and  $2^N$  tap points, the full-scale DAC register code is the resistor element (1 LSb) from the source reference voltage ( $V_{DD}$  or  $V_{REF}$ ).

### B.2 Least Significant Bit (LSb)

This is the voltage difference between two successive codes. For a given output voltage range, it is divided by the resolution of the device (Equation B-1). The range may be  $V_{DD}$  (or  $V_{REF}$ ) to  $V_{SS}$  (ideal), the DAC register codes across the linear range of the output driver (Measured 1), or full-scale to zero-scale (Measured 2).

# EQUATION B-1: LSb VOLTAGE CALCULATION

### **B.3** Monotonic Operation

Monotonic operation means that the device's output voltage ( $V_{OUT}$ ) increases with every 1 code step (LSb) increment (from  $V_{SS}$  to the DAC's reference voltage ( $V_{DD}$  or  $V_{REF}$ )).

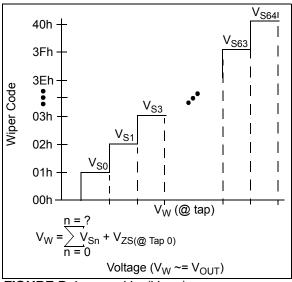


FIGURE B-1:  $V_W(V_{OUT})$ 

# B.4 Full-Scale Error (E<sub>FS</sub>)

The Full-Scale Error (see Figure B-3) is the error on the  $V_{OUT}$  pin relative to the expected  $V_{OUT}$  voltage (theoretical) for the maximum device DAC register code (code FFFh for 12-bit, code 3FFh for 10-bit, and code FFh for 8-bit) (see Equation B-2). The error is dependent on the resistive load on the  $V_{OUT}$  pin (and where that load is tied to, such as  $V_{SS}$  or  $V_{DD}$ ). For loads (to  $V_{SS}$ ) greater than specified, the full-scale error will be greater.

The error in bits is determined by the theoretical voltage step size to give an error in LSb.

### **EQUATION B-2: FULL-SCALE ERROR**

$$E_{FS} = \frac{V_{OUT(@FS)} - V_{IDEAL(@FS)}}{V_{LSb(IDEAL)}}$$

Where:

 $\mathsf{E}_{\mathsf{FS}}$  is expressed in LSb.

 $V_{OUT(@FS)}$  = The  $V_{OUT}$  voltage when the DAC register code is at full-scale.

V<sub>IDEAL(@FS)</sub> = The ideal output voltage when the DAC register code is at full-scale.

 $V_{LSb(IDEAL)}$  = The theoretical voltage step size.

### B.5 Zero-Scale Error (E<sub>ZS</sub>)

The Zero-Scale Error (see Figure B-2) is the difference between the ideal and measured  $V_{OUT}$  voltage with the DAC register code equal to 000h (Equation B-3). The error is dependent on the resistive load on the  $V_{OUT}$  pin (and where that load is tied to, such as  $V_{SS}$  or  $V_{DD}$ ). For loads (to  $V_{DD}$ ) greater than specified, the zero-scale error will be greater.

The error in bits is determined by the theoretical voltage step size to give an error in LSb.

### **EQUATION B-3: ZERO-SCALE ERROR**

$$E_{ZS} = \frac{V_{OUT(@ZS)}}{V_{LSb(IDEAL)}}$$

Where:

E<sub>7S</sub> is expressed in LSb.

 $V_{OUT(@ZS)}$  = The  $V_{OUT}$  voltage when the DAC register code is at Zero-scale.

 $V_{LSb(IDEAL)}$  = The theoretical voltage step size.

### B.6 Total Unadjusted Error $(E_T)$

The Total Unadjusted Error  $(E_T)$  is the difference between the ideal and measured  $V_{OUT}$  voltage. Typically, calibration of the output voltage is implemented to improve system performance.

The error in bits is determined by the theoretical voltage step size to give an error in LSb.

Equation B-4 shows the Total Unadjusted Error calculation.

# EQUATION B-4: TOTAL UNADJUSTED ERROR CALCULATION

$$E_T = \frac{(V_{OUT\_Actual(@code)} - V_{OUT\_Ideal(@Code)})}{V_{LSb(Ideal)}}$$

Where:

E<sub>T</sub> is expressed in LSb.

V<sub>OUT\_Actual(@code)</sub> = The measured DAC output voltage at the specified code.

V<sub>OUT\_Ideal(@code)</sub> = The calculated DAC output voltage at the specified code.

(code \* V<sub>LSb(Ideal)</sub>)

 $V_{LSb(Ideal)} = V_{REF} / \# Steps$ 

12-bit =  $V_{REF}/4096$ 10-bit =  $V_{REF}/1024$ 

8-bit =  $V_{REF}/256$ 

### B.7 Offset Error (E<sub>OS</sub>)

The offset error is the delta voltage of the  $V_{OUT}$  voltage from the ideal output voltage at the specified code. This code is specified where the output amplifier is in the linear operating range; for the MCP48FEBXX we specify code 100 (decimal). Offset error does not include gain error. Figure B-2 illustrates this.

This error is expressed in mV. Offset error can be negative or positive. The offset error can be calibrated by software in application circuits.

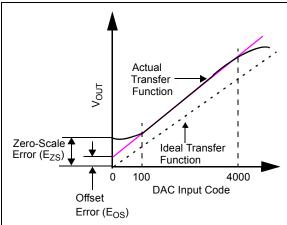


FIGURE B-2: Offset Error and Zero-Scale Error.

# B.8 Offset Error Drift (E<sub>OSD</sub>)

Offset error drift is the variation in offset error due to a change in ambient temperature. Offset error drift is typically expressed in ppm/ $^{o}$ C or  $\mu$ V/ $^{o}$ C.

### B.9 Gain Error $(E_G)$

Gain error is a calculation based on the ideal slope using the voltage boundaries for the linear range of the output driver (ex code 100 and code 4000) (see Figure B-3). The gain error calculation nullifies the device's offset error.

Gain error indicates how well the slope of the actual transfer function matches the slope of the ideal transfer function. Gain error is usually expressed as percent of full-scale range (% of FSR) or in LSb. FSR is the ideal full-scale voltage of the DAC (see Equation B-5).

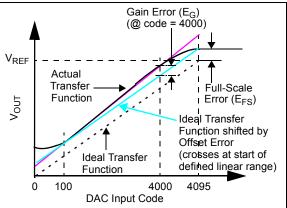


FIGURE B-3: Gain Error and Full-Scale Error Example.

### **EQUATION B-5: EXAMPLE GAIN ERROR**

$$E_G = \frac{\left( \ V_{OUT(@4000)} \cdot V_{OS} \cdot V_{OUT\_Ideal(@4000)} \right)}{V_{Full\text{-}Scale\ Range}} \bullet 100$$
 Where: 
$$E_G \text{ is expressed in } \% \text{ of full-scale range (FSR)}.$$
 
$$V_{OUT(@4000)} = \text{The measured DAC output voltage at the specified code}.$$
 
$$V_{OUT\_Ideal(@4000)} = \text{The calculated DAC output voltage at the specified code}.$$
 
$$\left( \ 4000 * V_{LSb(Ideal)} \right)$$
 
$$V_{OS} = \text{Measured offset voltage}.$$
 
$$V_{Full\ Scale\ Range} = \text{Expected full-scale output value (such as the } V_{REF} \text{ voltage}).}$$

# B.10 Gain-Error Drift (E<sub>GD</sub>)

Gain-error drift is the variation in gain error due to a change in ambient temperature. Gain error drift is typically expressed in ppm/°C (of full-scale range).

### **B.11** Integral Nonlinearity (INL)

The Integral Nonlinearity (INL) error is the maximum deviation of an actual transfer function from an ideal transfer function (straight line) passing through the defined end points of the DAC transfer function (after offset and gain errors have been removed).

In the MCP48FEBXX, INL is calculated using the defined end points, DAC code 100 and code 4000. INL can be expressed as a percentage of full-scale range (FSR) or in LSb. INL is also called Relative Accuracy. Equation B-6 shows how to calculate the INL error in LSb and Figure B-4 shows an example of INL accuracy.

Positive INL means higher  $V_{OUT}$  voltage than ideal. Negative INL means lower  $V_{OUT}$  voltage than ideal.

### **EQUATION B-6: INL ERROR**

 $E_{INL} = \frac{(V_{OUT} - V_{Calc\_Ideal})}{V_{LSb(Measured)}}$ 

Where:

INL is expressed in LSb.

 $V_{Calc\_Ideal}$  = Code \*  $V_{LSb(Measured)}$  +  $V_{OS}$ 

V<sub>OUT(Code = n)</sub> = The measured DAC output voltage with a given DAC

voltage with a given DAC

register code

 $V_{LSb(Measured)}$  = For Measured:

(V<sub>OUT(4000)</sub> - V<sub>OUT(100)</sub>)/3900

 $V_{OS}$  = Measured offset voltage.

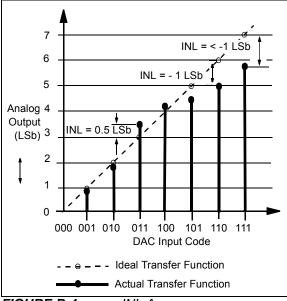


FIGURE B-4: INL Accuracy.

### **B.12** Differential Nonlinearity (DNL)

The Differential Nonlinearity (DNL) error (see Figure B-5) is the measure of step size between codes in actual transfer function. The ideal step size between codes is 1 LSb. A DNL error of zero would imply that every code is exactly 1 LSb wide. If the DNL error is less than 1 LSb, the DAC guarantees monotonic output and no missing codes. Equation B-7 shows how to calculate the DNL error between any two adjacent codes in LSb.

### **EQUATION B-7: DNL ERROF**

$$E_{DNL} = \frac{(V_{OUT(code = n+1)} - V_{OUT(code = n)})}{V_{LSb(Measured)}} - 1$$

Where:

DNL is expressed in LSb.

 $V_{OUT(Code = n)}$  = The measured DAC output voltage

with a given DAC register code.

 $V_{LSb(Measured)}$  = For Measured:

(V<sub>OUT(4000)</sub> - V<sub>OUT(100)</sub>)/3900

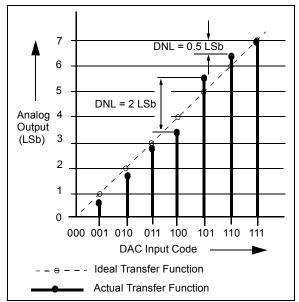


FIGURE B-5: DNL Accuracy.

### **B.13** Settling Time

Settling time is the time delay required for the  $V_{OUT}$  voltage to settle into its new output value. This time is measured from the start of code transition to when the  $V_{OUT}$  voltage is within the specified accuracy.

In the MCP48FEBXX, the settling time is a measure of the time delay until the  $V_{OUT}$  voltage reaches within 0.5 LSb of its final value, when the volatile DAC Register changes from 1/4 to 3/4 of the full-scale range (12-bit device: 400h to C00h).

### **B.14** Major-Code Transition Glitch

Major-Code transition glitch is the impulse energy injected into the DAC analog output when the code in the DAC register changes state. It is normally specified as the area of the glitch in nV-Sec, and is measured when the digital code is changed by 1 LSb at the major carry transition.

Example: 011...111 to 100...000 or 100...000 to 011...111

### B.15 Digital Feed-through

Digital feed-through is the glitch that appears at the analog output, caused by coupling from the digital input pins of the device. The area of the glitch is expressed in nV-Sec, and is measured with a full-scale change on the digital input pins.

Example: all 0s to all 1s and vice versa.

The digital feed-through is measured when the DAC is not being written to the output register.

### B.16 -3 dB Bandwidth

This is the frequency of the signal at the  $V_{REF}$  pin that causes the voltage at the  $V_{OUT}$  pin to fall -3 dB value from a static value on the  $V_{REF}$  pin. The output decreases due to the RC characteristics of the resistor ladder and the characteristics of the output buffer.

### **B.17 Power-Supply Sensitivity (PSS)**

PSS indicates how the output of the DAC is affected by changes in the supply voltage. PSS is the ratio of the change in  $V_{OUT}$  to a change in  $V_{DD}$  for mid-scale output of the DAC. The  $V_{OUT}$  is measured while the  $V_{DD}$  is varied from 5.5V to 2.7V as a step ( $V_{REF}$  voltage held constant), and expressed in %/%, which is the % change of the DAC output voltage with respect to the % change of the  $V_{DD}$  voltage.

### **EQUATION B-8: PSS CALCULATION**

$$PSS = \frac{\frac{V_{OUT(@5.5V)} - V_{OUT(@2.7V)}}{V_{OUT(@5.5V)}}}{\frac{(5.5V - 2.7V)}{5.5V}}$$

Where:

PSS is expressed in %/%.

 $V_{OUT(@5.5V)}$  = The measured DAC output voltage with  $V_{DD}$  = 5.5V.

 $V_{OUT(@2.7V)}$  = The measured DAC output voltage with  $V_{DD}$  = 2.7V.

# B.18 Power-Supply Rejection Ratio (PSRR)

PSRR indicates how the output of the DAC is affected by changes in the supply voltage. PSRR is the ratio of the change in  $V_{OUT}$  to a change in  $V_{DD}$  for full-scale output of the DAC. The  $V_{OUT}$  is measured while the  $V_{DD}$  is varied  $\pm$  10% ( $V_{REF}$  voltage held constant), and expressed in dB or  $\mu V/V$ .

### **B.19** V<sub>OUT</sub> Temperature Coefficient

The V<sub>OUT</sub> Temperature Coefficient quantifies the error in the resistor ladder's resistance ratio (DAC Register code value) and Output Buffer due to temperature drift.

### **B.20** Absolute Temperature Coefficient

The absolute temperature coefficient quantifies the error in the end-to-end output voltage (Nominal output voltage  $V_{OUT}$ ) due to temperature drift. For a DAC this error is typically not an issue due to the ratiometric aspect of the output.

### **B.21 Noise Spectral Density**

Noise spectral density is a measurement of the device's internally-generated random noise, and is characterized as a spectral density (voltage per  $\sqrt{\text{Hz}}$ ). It is measured by loading the DAC to the mid-scale value and measuring the noise at the  $V_{OUT}$  pin. It is measured in  $nV/\sqrt{\text{Hz}}$ .

# PRODUCT IDENTIFICATION SYSTEM

 $\underline{\text{To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.}\\$ 

	v(1)	Examples:			
PART NO. Device	X <sup>(1)</sup> X — /XX Tape and Temperature Package Reel Range	a) MCP48FEB01-E/UN:  8-bit V <sub>OUT</sub> resolution, Single Channel, Tube, Extended Temperature., 10-Lead MSOP Package  b) MCP48FEB01T-E/UN:  8-bit V <sub>OUT</sub> resolution, Single			
Device:	MCP48FEB01: Single-Channel 8-Bit NV DAC with External + Internal References	Channel, Tape and Reel, Extended Temperature, 10-Lead MSOP Package			
	MCP48FEB02: Dual-Channel 8-Bit NV DAC with External + Internal References	a) MCP48FEB11-E/UN: 10-bit V <sub>OUT</sub> resolution, Single			
	MCP48FEB11: Single-Channel 10-Bit NV DAC with External + Internal References	Channel, Tube, Extended Temperature, 10-Lead MSOP Package			
	MCP48FEB12: Dual-Channel 10-Bit NV DAC with External + Internal References	b) MCP48FEB11T-E/UN: 10-bit V <sub>OUT</sub> resolution, Single Channel, Tape and Reel, Extended Temperature,			
	MCP48FEB21: Single-Channel 12-Bit NV DAC with External + Internal References	10-Lead MSOP Package			
MCP48FEB22: Dual-Channel 12-Bit NV DAC with External + Internal References		a) MCP48FEB21-E/UN: 12-bit V <sub>OUT</sub> resolution, Single Channel, Tube, Extended Temperature, 10-Lead MSOP			
Tape and Reel:	T = Tape and Reel <sup>(1)</sup> Blank = Tube	b) MCP48FEB21T-E/UN: 12-bit V <sub>OUT</sub> resolution, Single Channel, Tape and Reel, Extended Temperature, 10-Lead MSOP Package			
Temperature Range:	E = -40°C to +125°C (Extended)	a) MCP48FEB22-E/UN: 12-bit V <sub>OUT</sub> resolution, Dual Channel, Tube, Extended Temperature, 10-Lead MSOP Package			
Package:	UN = Plastic Micro Small Outline (MSOP), 10-Lead	b) MCP48FEB22T-E/UN: 12-bit V <sub>OUT</sub> resolution, Dual Channel, Tape and Reel, Extended Temperature, 10-Lead MSOP Package			
		Note 1: Tape and Reel identifier only appears in the catalog part number description. This identifier is used for ordering purposes and is not printed on the device package. Check with your Microchip sales office for package availability for the Tape and Reel option.			

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